

209-Bump BGA  
Commercial Temp  
Industrial Temp



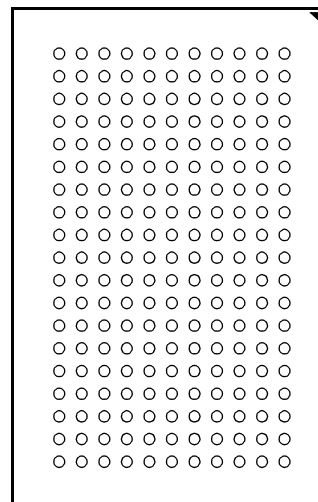
# 18Mb $\Sigma$ 1x1 MultiMode SRAM

## 1M x 18, 512K x 36, 256K x 72

250 - 333 MHz  
1.8 V  $V_{DD}$   
1.8 V and 1.5 V I/O

## Features

- User-configurable Early, Late and Double Late Write mode
- User-configurable pipelined and flow through operation
- JEDEC standard SigmaRAM™ pinout and package
- 1.8 V +150/-100 mV core power supply
- 1.5 V or 1.8 V I/O supply
- Dual Cycle Deselect in Pipeline mode
- Burst Synchronous operation
- Fully coherent read and write pipelines
- Echo Clock outputs track data output drivers in Pipeline mode
- ZQ mode pin for user-selectable output drive strength
- Byte write operation (9-bit bytes)
- 2 User programmable chip enable inputs for easy depth expansion.
- IEEE 1149.1 JTAG-compatible Boundary Scan
- 209-bump, 14 mm x 22 mm, 1 mm bump pitch BGA package
- Pin compatible with future 32M, 64M, and 128M devices



**Bottom View**

**209-Bump, 14 mm x 22 mm BGA  
1 mm Bump Pitch, 11 x 19 Bump Array**

		- 333
Pipeline mode	tKHKH	3.0 ns
	tKHQV	1.5 ns
Flow Through mode	tKHKH	5 ns
	tKHQV	5 ns

## SigmaRAM Family Overview

GS8170S18/36/72 SigmaRAMs are built in compliance with the SigmaRAM pinout standard for synchronous SRAMs. They are 18,874,368-bit (18Mb) SRAMs. These are the first in a family of wide, very low voltage CMOS I/O SRAMs designed to operate at the speeds needed to implement economical high performance networking systems.

GSI's  $\Sigma$ RAMs are offered in a number of configurations that emulate other synchronous SRAMs, such as Burst RAMs, NBT, Late Write, or Double Data Rate (DDR) SRAMs. The logical differences between the protocols employed by these RAMs hinge mainly on various combinations of address bursting, output data registering and write cueing. The  $\Sigma$ RAM™ family standard allows a user to implement the interface protocol best suited to the task at hand.

## Functional Description

Because SigmaRAMs are synchronous devices, address, data inputs, and read/write control inputs are captured on the rising edge of the input clock. Write cycles are internally self-timed and initiated by the rising edge of the clock input. This feature eliminates complex off-chip write pulse generation required by asynchronous SRAMs and simplifies input signal timing.

A  $\Sigma$ RAM may be configured by the user to read in Pipeline or Flow Through mode. In Pipeline mode, single data rate  $\Sigma$ RAMs incorporate a rising-edge-triggered output register. For read cycles, a pipelined SRAM's output data is staged at the input of an edge-triggered output register during the access cycle and then released to the output drivers at the next rising edge of clock.

GS817x18/36/72B  $\Sigma$ RAMs are implemented with GSI's high performance CMOS technology and are packaged in a 209-bump BGA.

## 8170S72B 256K x 72 Pinout

## 256K x 72 Common I/O—Top View

	1	2	3	4	5	6	7	8	9	10	11
A	DQg	DQg	A	E2	A (16M)	ADV	A (8M)	E3	A	DQb	DQb
B	DQg	DQg	Bc	Bg	NC	W	A	Bb	Bf	DQb	DQb
C	DQg	DQg	Bh	Bd	NC (128M)	E1	NC	Be	Ba	DQb	DQb
D	DQg	DQg	V <sub>SS</sub>	NC	NC	MCL	NC	NC	V <sub>SS</sub>	DQb	DQb
E	DQPg	DQPc	V <sub>DDQ</sub>	V <sub>DDQ</sub>	V <sub>DD</sub>	V <sub>DD</sub>	V <sub>DD</sub>	V <sub>DDQ</sub>	V <sub>DDQ</sub>	DQPf	DQPb
F	DQc	DQc	V <sub>SS</sub>	V <sub>SS</sub>	V <sub>SS</sub>	ZQ	V <sub>SS</sub>	V <sub>SS</sub>	V <sub>SS</sub>	DQf	DQf
G	DQc	DQc	V <sub>DDQ</sub>	V <sub>DDQ</sub>	V <sub>DD</sub>	EP2	V <sub>DD</sub>	V <sub>DDQ</sub>	V <sub>DDQ</sub>	DQf	DQf
H	DQc	DQc	V <sub>SS</sub>	V <sub>SS</sub>	V <sub>SS</sub>	EP3	V <sub>SS</sub>	V <sub>SS</sub>	V <sub>SS</sub>	DQf	DQf
J	DQc	DQc	V <sub>DDQ</sub>	V <sub>DDQ</sub>	V <sub>DD</sub>	M4	V <sub>DD</sub>	V <sub>DDQ</sub>	V <sub>DDQ</sub>	DQf	DQf
K	CQ2	CQ2	CK	NC	V <sub>SS</sub>	MCL	V <sub>SS</sub>	NC	NC	CQ1	CQ1
L	DQh	DQh	V <sub>DDQ</sub>	V <sub>DDQ</sub>	V <sub>DD</sub>	M2	V <sub>DD</sub>	V <sub>DDQ</sub>	V <sub>DDQ</sub>	DQa	DQa
M	DQh	DQh	V <sub>SS</sub>	V <sub>SS</sub>	V <sub>SS</sub>	M3	V <sub>SS</sub>	V <sub>SS</sub>	V <sub>SS</sub>	DQa	DQa
N	DQh	DQh	V <sub>DDQ</sub>	V <sub>DDQ</sub>	V <sub>DD</sub>	SD	V <sub>DD</sub>	V <sub>DDQ</sub>	V <sub>DDQ</sub>	DQa	DQa
P	DQh	DQh	V <sub>SS</sub>	V <sub>SS</sub>	V <sub>SS</sub>	MCL	V <sub>SS</sub>	V <sub>SS</sub>	V <sub>SS</sub>	DQa	DQa
R	DQPd	DQPh	V <sub>DDQ</sub>	V <sub>DDQ</sub>	V <sub>DD</sub>	V <sub>DD</sub>	V <sub>DD</sub>	V <sub>DDQ</sub>	V <sub>DDQ</sub>	DQPa	DQPe
T	DQd	DQd	V <sub>SS</sub>	NC	NC	MCL	NC	NC	V <sub>SS</sub>	DQe	DQe
U	DQd	DQd	NC	A	NC (64M)	A	NC (32M)	A	NC	DQe	DQe
V	DQd	DQd	A	A	A	A1	A	A	A	DQe	DQe
W	DQd	DQd	TMS	TDI	A	A0	A	TDO	TCK	DQe	DQe

• 2001.03

11 x 19 Bump BGA—14 x 22 mm<sup>2</sup> Body—1 mm Bump Pitch

## 8170S36B 512K x 36 Pinout

## 512K x 36 Common I/O—Top View

	1	2	3	4	5	6	7	8	9	10	11
A	NC	NC	A	E2	A (16M)	ADV	A	E3	A	DQb	DQb
B	NC	NC	Bc	NC	A	W	A	Bb	NC	DQb	DQb
C	NC	NC	NC	Bd	NC (128M)	E1	NC	NC	Ba	DQb	DQb
D	NC	NC	V <sub>SS</sub>	NC	NC	MCL	NC	NC	V <sub>SS</sub>	DQb	DQb
E	NC	DQPc	V <sub>DDQ</sub>	V <sub>DDQ</sub>	V <sub>DD</sub>	V <sub>DD</sub>	V <sub>DD</sub>	V <sub>DDQ</sub>	V <sub>DDQ</sub>	NC	DQPb
F	DQc	DQc	V <sub>SS</sub>	V <sub>SS</sub>	V <sub>SS</sub>	ZQ	V <sub>SS</sub>	V <sub>SS</sub>	V <sub>SS</sub>	NC	NC
G	DQc	DQc	V <sub>DDQ</sub>	V <sub>DDQ</sub>	V <sub>DD</sub>	EP2	V <sub>DD</sub>	V <sub>DDQ</sub>	V <sub>DDQ</sub>	NC	NC
H	DQc	DQc	V <sub>SS</sub>	V <sub>SS</sub>	V <sub>SS</sub>	EP3	V <sub>SS</sub>	V <sub>SS</sub>	V <sub>SS</sub>	NC	NC
J	DQc	DQc	V <sub>DDQ</sub>	V <sub>DDQ</sub>	V <sub>DD</sub>	M4	V <sub>DD</sub>	V <sub>DDQ</sub>	V <sub>DDQ</sub>	NC	NC
K	CQ2	CQ2	CK	NC	V <sub>SS</sub>	MCL	V <sub>SS</sub>	NC	NC	CQ1	CQ1
L	NC	NC	V <sub>DDQ</sub>	V <sub>DDQ</sub>	V <sub>DD</sub>	M2	V <sub>DD</sub>	V <sub>DDQ</sub>	V <sub>DDQ</sub>	DQa	DQa
M	NC	NC	V <sub>SS</sub>	V <sub>SS</sub>	V <sub>SS</sub>	M3	V <sub>SS</sub>	V <sub>SS</sub>	V <sub>SS</sub>	DQa	DQa
N	NC	NC	V <sub>DDQ</sub>	V <sub>DDQ</sub>	V <sub>DD</sub>	SD	V <sub>DD</sub>	V <sub>DDQ</sub>	V <sub>DDQ</sub>	DQa	DQa
P	NC	NC	V <sub>SS</sub>	V <sub>SS</sub>	V <sub>SS</sub>	MCL	V <sub>SS</sub>	V <sub>SS</sub>	V <sub>SS</sub>	DQa	DQa
R	DQPd	NC	V <sub>DDQ</sub>	V <sub>DDQ</sub>	V <sub>DD</sub>	V <sub>DD</sub>	V <sub>DD</sub>	V <sub>DDQ</sub>	V <sub>DDQ</sub>	DQPd	NC
T	DQd	DQd	V <sub>SS</sub>	NC	NC	MCL	NC	NC	V <sub>SS</sub>	NC	NC
U	DQd	DQd	NC	A	NC (64M)	A	NC (32M)	A	NC	NC	NC
V	DQd	DQd	A	A	A	A1	A	A	A	NC	NC
W	DQd	DQd	TMS	TDI	A	A0	A	TDO	TCK	NC	NC

• 2001.03

11 x 19 Bump BGA—14 x 22 mm<sup>2</sup> Body—1 mm Bump Pitch

## 8170S18 1M x 18 Pinout

## 1M x 18 Common I/O—Top View

	1	2	3	4	5	6	7	8	9	10	11
A	NC	NC	A	E2	A (16M)	ADV	A	E3	A	NC	NC
B	NC	NC	Bb	NC	A	W	A	NC	NC	NC	NC
C	NC	NC	NC	NC	NC (128M)	E1	A	NC	Ba	NC	NC
D	NC	NC	V <sub>SS</sub>	NC	NC	MCL	NC	NC	V <sub>SS</sub>	NC	NC
E	NC	DQPb	V <sub>DDQ</sub>	V <sub>DDQ</sub>	V <sub>DD</sub>	V <sub>DD</sub>	V <sub>DD</sub>	V <sub>DDQ</sub>	V <sub>DDQ</sub>	NC	NC
F	DQb	DQb	V <sub>SS</sub>	V <sub>SS</sub>	V <sub>SS</sub>	ZQ	V <sub>SS</sub>	V <sub>SS</sub>	V <sub>SS</sub>	NC	NC
G	DQb	DQb	V <sub>DDQ</sub>	V <sub>DDQ</sub>	V <sub>DD</sub>	EP2	V <sub>DD</sub>	V <sub>DDQ</sub>	V <sub>DDQ</sub>	NC	NC
H	DQb	DQb	V <sub>SS</sub>	V <sub>SS</sub>	V <sub>SS</sub>	EP3	V <sub>SS</sub>	V <sub>SS</sub>	V <sub>SS</sub>	NC	NC
J	DQb	DQb	V <sub>DDQ</sub>	V <sub>DDQ</sub>	V <sub>DD</sub>	M4	V <sub>DD</sub>	V <sub>DDQ</sub>	V <sub>DDQ</sub>	NC	NC
K	CQ2	CQ2	CK	NC	V <sub>SS</sub>	MCL	V <sub>SS</sub>	NC	NC	CQ1	CQ1
L	NC	NC	V <sub>DDQ</sub>	V <sub>DDQ</sub>	V <sub>DD</sub>	M2	V <sub>DD</sub>	V <sub>DDQ</sub>	V <sub>DDQ</sub>	DQa	DQa
M	NC	NC	V <sub>SS</sub>	V <sub>SS</sub>	V <sub>SS</sub>	M3	V <sub>SS</sub>	V <sub>SS</sub>	V <sub>SS</sub>	DQa	DQa
N	NC	NC	V <sub>DDQ</sub>	V <sub>DDQ</sub>	V <sub>DD</sub>	SD	V <sub>DD</sub>	V <sub>DDQ</sub>	V <sub>DDQ</sub>	DQa	DQa
P	NC	NC	V <sub>SS</sub>	V <sub>SS</sub>	V <sub>SS</sub>	MCL	V <sub>SS</sub>	V <sub>SS</sub>	V <sub>SS</sub>	DQa	DQa
R	NC	NC	V <sub>DDQ</sub>	V <sub>DDQ</sub>	V <sub>DD</sub>	V <sub>DD</sub>	V <sub>DD</sub>	V <sub>DDQ</sub>	V <sub>DDQ</sub>	DQP <sub>a</sub>	NC
T	NC	NC	V <sub>SS</sub>	NC	NC	MCL	NC	NC	V <sub>SS</sub>	NC	NC
U	NC	NC	NC	A	NC (64M)	A	NC (32M)	A	NC	NC	NC
V	NC	NC	A	A	A	A1	A	A	A	NC	NC
W	NC	NC	TMS	TDI	A	A0	A	TDO	TCK	NC	NC

• 2001.03

11 x 19 Bump BGA—14 x 22 mm<sup>2</sup> Body—1 mm Bump Pitch

## Pin Description Table

Pin Location	Symbol	Description	Type	Comments
A3, A5, A7, A9, B7, U4, U6, U8, V3, V4, V5, V6, V7, V8, V9, W5, W6, W7	A	Address	Input	—
C7	A	Address	Input	x18 version only
B5	A	Address	Input	x18 and x36 versions
A6	ADV	Advance	Input	Active High
B3, C9	$\overline{Bx}$	Byte Write Enable	Input	Active Low (all versions)
B8, C4	$\overline{Bx}$	Byte Write Enable	Input	Active Low (x36 and x72 versions)
B4, B9, C3, C8	$\overline{Bx}$	Byte Write Enable	Input	Active Low (x72 version only)
K3	CK	Clock	Input	Active High
K1, K11	CQ	Echo Clock	Output	Active High
K2, K10	$\overline{CQ}$	Echo Clock	Output	Active Low
E2, F1, F2, G1, G2, H1, H2, J1, J2, L10, L11, M10, M11, N10, N11, P10, P11, R10	DQ	Data I/O	Input/Output	x18, x36, and x72 versions
A10, A11, B10, B11, C10, C11, D10, D11, E11, R1, T1, T2, U1, U2, V1, V2, W1, W2	DQ	Data I/O	Input/Output	x36 and x72 versions
A1, A2, B1, B2, C1, C2, D1, D2, E1, E10, F10, F11, G10, G11, H10, H11, J10, J11, L1, L2, M1, M2, N1, N2, P1, P2, R2, R11, T10, T11, U10, U11, V10, V11, W10, W11	DQ	Data I/O	Input/Output	x72 version only
C6	$\overline{E1}$	Chip Enable	Input	Active Low
A4, A8	E2 & E3	Chip Enable	Input	Programmable Active High or Low
G6, H6	EP2 & EP3	Chip Enable Program Pin	Input	—
W9	TCK	Test Clock	Input	Active High
W4	TDI	Test Data In	Input	—
W8	TDO	Test Data Out	Output	—
W3	TMS	Test Mode Select	Input	—
L6, M6, J6	M2, M3 & M4	Mode Control Pins	Input	—
N6	$\overline{SD}$	Slow Down	Input	Active Low

Pin Description Table

Pin Location	Symbol	Description	Type	Comments
B3, C9, D6, K6, P6, T6, W6	MCL	Must Connect Low	Input	Active Low
C5, D4, D5, D7, D8, K4, K8, K9, T4, T5, T7, T8, U3, U5, U7, U9	NC	No Connect	—	Not connected to die (all versions)
B5	NC	No Connect	—	Not connected to die (x72 version)
C7	NC	No Connect	—	Not connected to die (x72/x36 versions)
A1, A2, B1, B2, B4, B9, C1, C2, C3, C8, D1, D2, E1, E10, F10, F11, G10, G11, H10, H11, J10, J11, L1, L2, M1, M2, N1, N2, P1, P2, R2, R11, T10, T11, U10, U11, V10, V11, W10, W11	NC	No Connect	—	Not connected to die (x36/x18 versions)
A10, A11, B8, B10, B11, C4, C10, C11, D10, D11, E11, R1, T1, T2, U1, U2, V1, V2, W1, W2	NC	No Connect	—	Not connected to die (x18 version)
B6	$\overline{W}$	Write	Input	Active Low
E5, E6, E7, G5, G7, J5, J7, L5, L7, N5, N7, R5, R6, R7	$V_{DD}$	Core Power Supply	Input	1.8 V Nominal
E3, E4, E8, E9, J3, J4, J8, J9, L3, L4, L8, L9, N3, N4, N8, N9, R3, R4, R8, R9	$V_{DDQ}$	Output Driver Power Supply	Input	1.8 V or 1.5 V Nominal
D3, D9, F3, F4, F5, F7, F8, F9, H3, H4, H5, H7, H8, H9, K5, K7, M3, M4, M5, M7, M8, M9, P3, P4, P5, P7, P8, P9, T3, T9	$V_{SS}$	Ground	Input	—
F6	ZQ	Output Impedance Control	Input	Low = Low Impedance [High Drive] High = High Impedance [Low Drive]

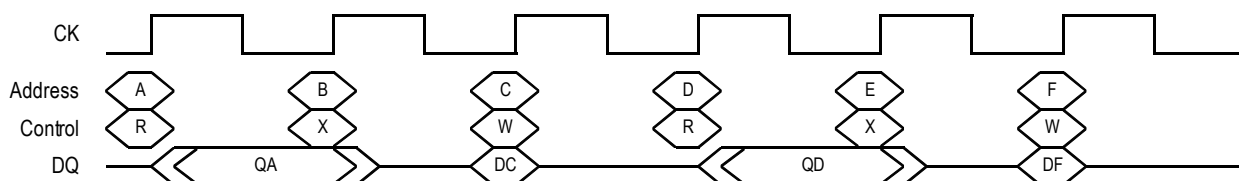
## **Background**

The central characteristics of  $\Sigma$ RAMs are that they are extremely fast and consume very little power. Because both operating and interface power is low,  $\Sigma$ RAMs can be implemented in a wide (x72) configuration, providing very high single package bandwidth (in excess of 20 Gb/s in ordinary pipelined configuration) and very low random access latency (5 ns). The use of very low voltage circuits in the core and 1.8 V or 1.5 V interface voltages allow the speed, power and density performance of  $\Sigma$ RAMs.

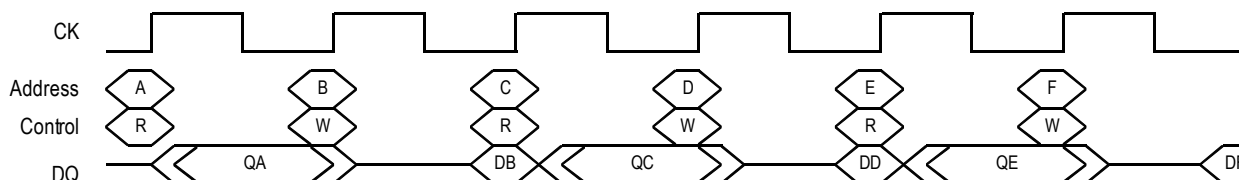
Although the SigmaRAM family of pinouts has been designed to support a number of different common read and write protocol options, not all SigmaRAM implementations will support all possible protocols. The following timing diagrams provide a quick comparison between read and write protocols options available in the context of the SigmaRAM standard. This particular data sheet covers the single data rate (non-DDR), SigmaRAM.

# Common I/O SigmaRAM Family Mode Comparison—EW vs. LW vs. DLW

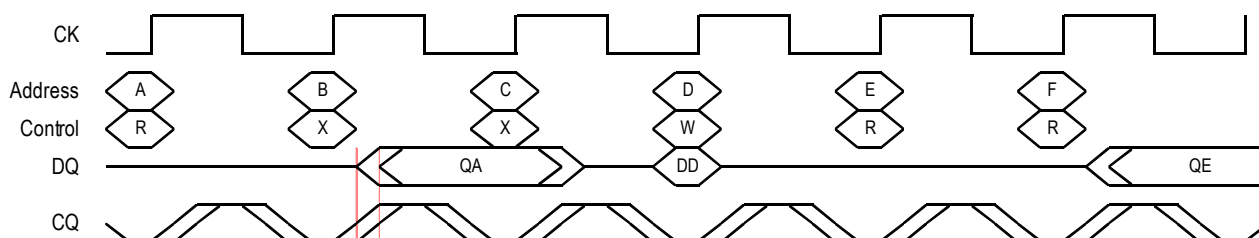
## $\Sigma 1x1Ef$ (Early Write - Flow Through Read)



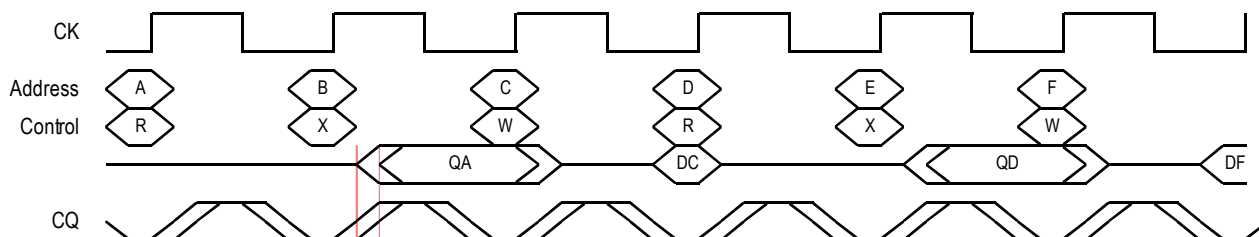
## $\Sigma 1x1Lf$ (Late Write - Flow Through Read)



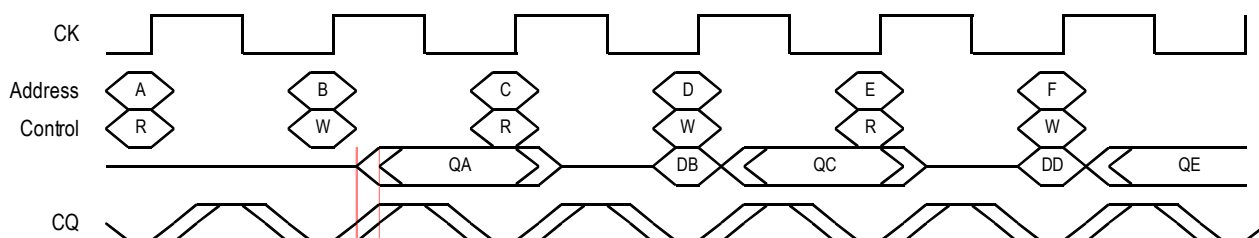
## $\Sigma 1x1Ep$ (Early Write - Pipelined Read)



## $\Sigma 1x1Lp$ (Late Write - Pipelined Read)



## $\Sigma 1x1Dp$ (Double Late Write - Pipelined Read)



The character of the applications for fast synchronous SRAMs in networking systems are extremely diverse.  $\Sigma$ RAMs have been developed to address the diverse needs of the networking market in a manner that can be supported with a unified development and manufacturing infrastructure.  $\Sigma$ RAMs address each of the bus protocol options commonly found in networking systems. This allows the  $\Sigma$ RAM to find application in radical shrinks and speed-ups of existing networking chip sets that were designed for use with older SRAMs, like the NBT, Late Write, or Double Data Rate SRAMs, as well as with new chip sets and ASIC's that employ the Echo Clocks and realize the full potential of the  $\Sigma$ RAMs.



# Mode Selection Truth Table Standard

M2	M3	M4	Name	Function	Analogous to...	In This Data Sheet?
0	0	0	$\Sigma 1x1Ef$	Early Write, Flow through Read	Flow through Burst RAM	Yes
0	0	1	$\Sigma 1x1Lf$	Late Write, Flow through Read	Flow through NBT SRAM	Yes
0	1	0		RFU		n/a
0	1	1	$\Sigma 1x2Lp$	DDR	Double Data Rate SRAM	No
1	0	0	$\Sigma 1x1Ep$	Early Write, Pipelined Read	Pipelined Burst RAM	Yes
1	0	1	$\Sigma 1x1Dp$	Double Late Write, Pipelined Read	Pipelined NBT SRAM	Yes
1	1	0	$\Sigma 1x1Lp$	Late Write, Pipelined Read	Pipelined Late Write SRAM	Yes
1	1	1		RFU	—	n/a

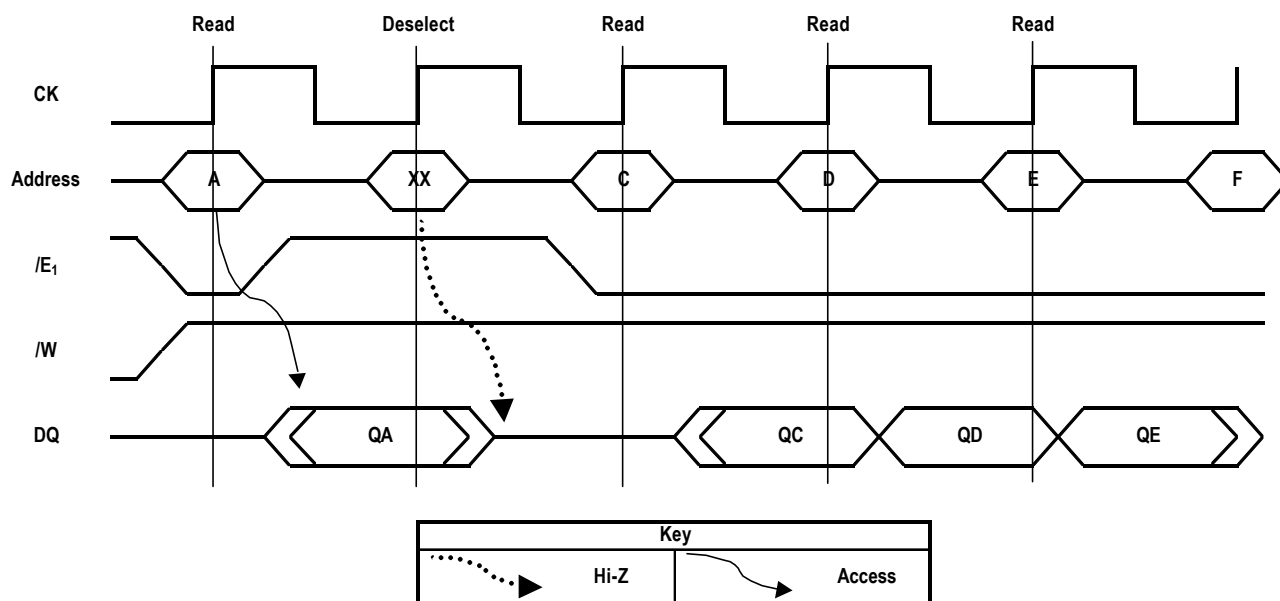
All address, data and control inputs (with the exception of PE2, PE3, and the mode pins, M2–M4) are synchronized to rising clock edges. Read and write operations must be initiated with the Advance/Load pin (ADV) held low, in order to load the new address. Device activation is accomplished by asserting all three of the Chip Enable inputs ( $\overline{E1}$ , E2, and E3). Deassertion of any one of the Enable inputs will deactivate the device. **It should be noted that ONLY deactivation of the RAM via E2 and/or E3 deactivates the Echo Clocks, CQ1–CQn.**

## Read Operations

### Flow Through Read

A Flow Through Read cycle sends data to the output drivers immediately after the address and read command are captured in the input registers. The main clock input, CK, need not ever fire again for data to be driven out. Normally, Flow Through mode is employed in situations where the latency of the RAM (the Flow Through tKHQV) is appreciably shorter than the bus frequency of the application.

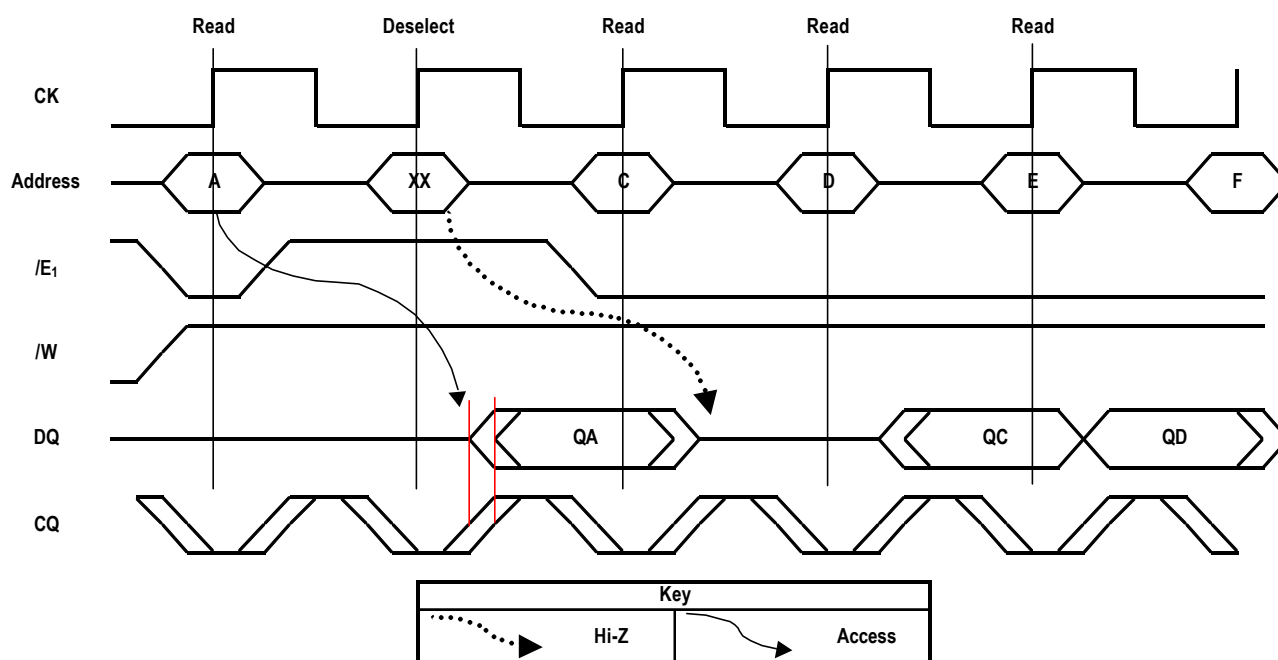
### Flow Through Read



## Pipelined Read

Read operation is initiated when the following conditions are satisfied at the rising edge of clock: All three chip enables ( $\overline{E1}$ , E2, and E3) are active, the write enable input signal ( $\overline{W}$ ) is deasserted high, and ADV is asserted low. The address presented to the address inputs is latched into the address register and presented to the memory core and control logic. The control logic determines that a read access is in progress and allows the requested data to propagate to the input of the output register. At the next rising edge of clock the read data is allowed to propagate through the output register and onto the output pins.

### Single Data Rate Pipelined Read



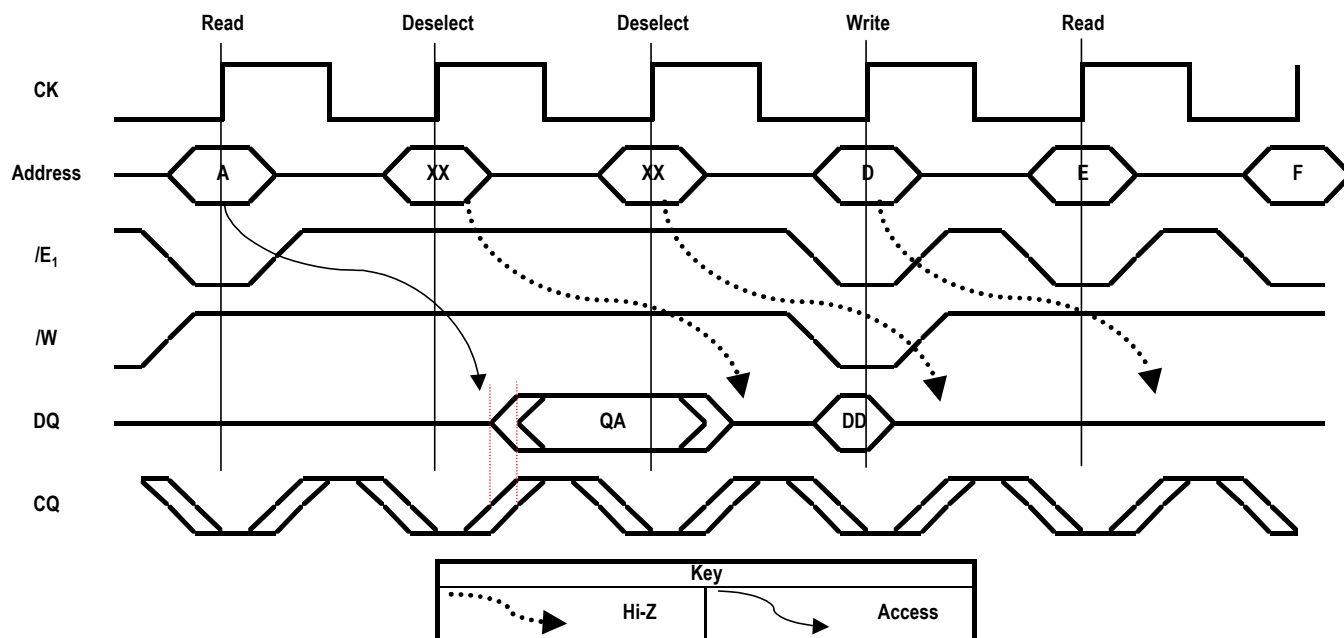
## Write Operations

Write operation occurs when the following conditions are satisfied at the rising edge of clock: All three chip enables ( $\overline{E1}$ , E2, and E3) are active and the write enable input signal ( $\overline{W}$ ) is asserted low.

## Early Write

The classic “PB” (Pipelined Burst) SRAMs employed the “Early Write” protocol. This is to say that Address, Control (the write command), and Data In are all required on the same clock edge.

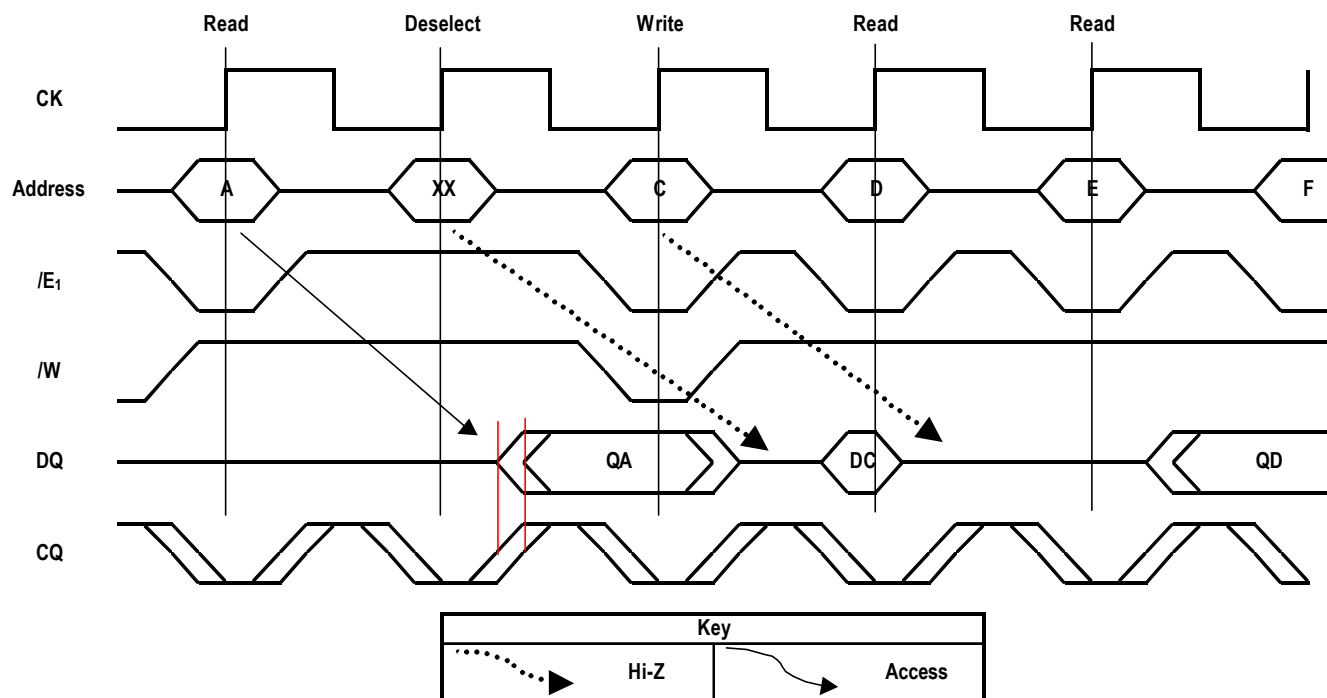
### SigmaRAM Early Write with Pipelined Read



## Late Write

In Late Write mode the RAM requires Data In one rising clock edge later than the edge used to load Address and Control. Late Write protocol has been employed on SRAMs designed for RISC processor L2 cache applications and in Flow Through mode NBT SRAMs.

### SigmaRAM Late Write with Pipelined Read



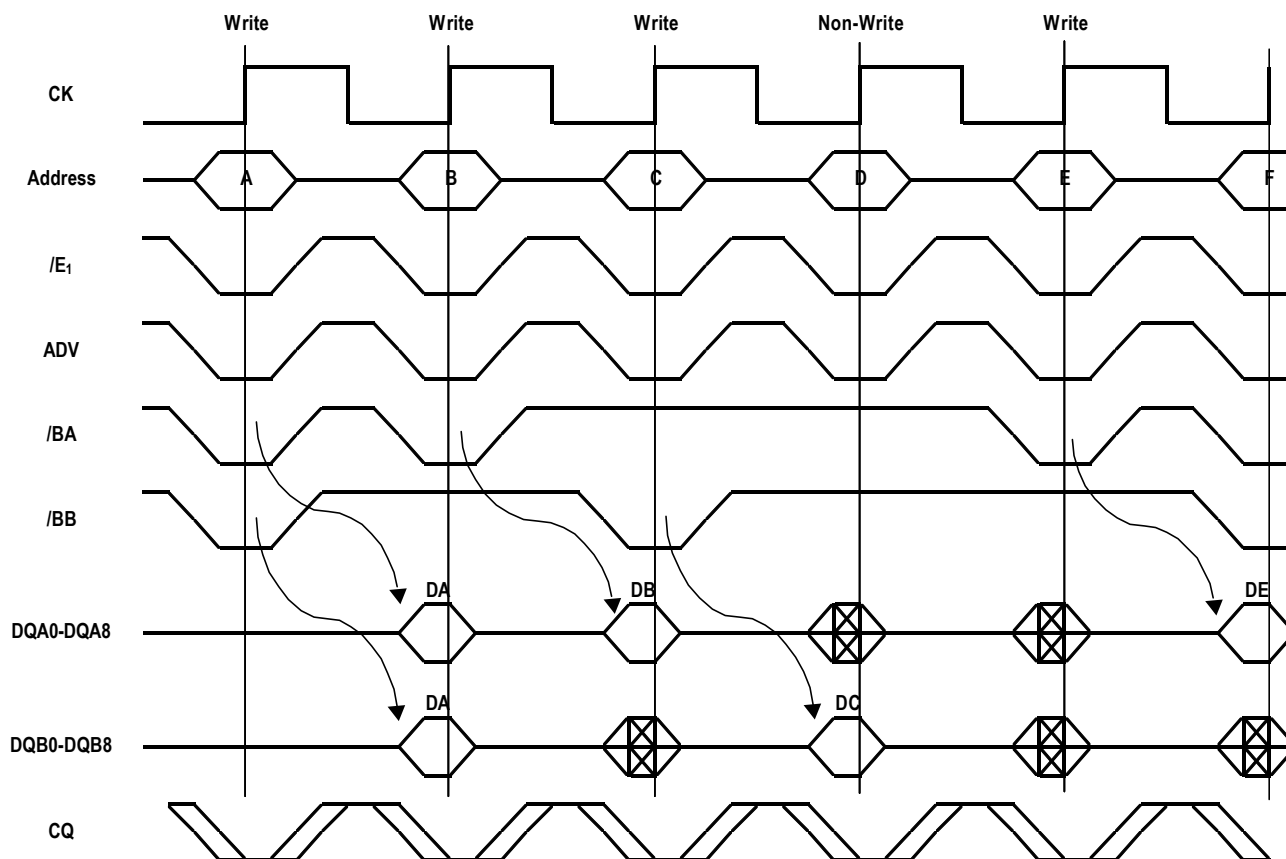
## Byte Write Control

The Byte Write Enable inputs ( $\overline{B}_X$ ) determine which bytes will be written. All or none may be activated. A Write Cycle with no Byte Write inputs active is a no-op cycle.

### Byte Write Truth Table

Function	$\overline{W}$	$\overline{B}_A$	$\overline{B}_B$	$\overline{B}_C$	$\overline{B}_D$
Read	H	X	X	X	X
Write Byte A	L	L	H	H	H
Write Byte B	L	H	L	H	H
Write Byte C	L	H	H	L	H
Write Byte D	L	H	H	H	L
Write all Bytes	L	L	L	L	L
Write Abort/NOP	L	H	H	H	H

### Byte Write Control Example with x18 SigmaRAM Late Write RAM



## Special Functions

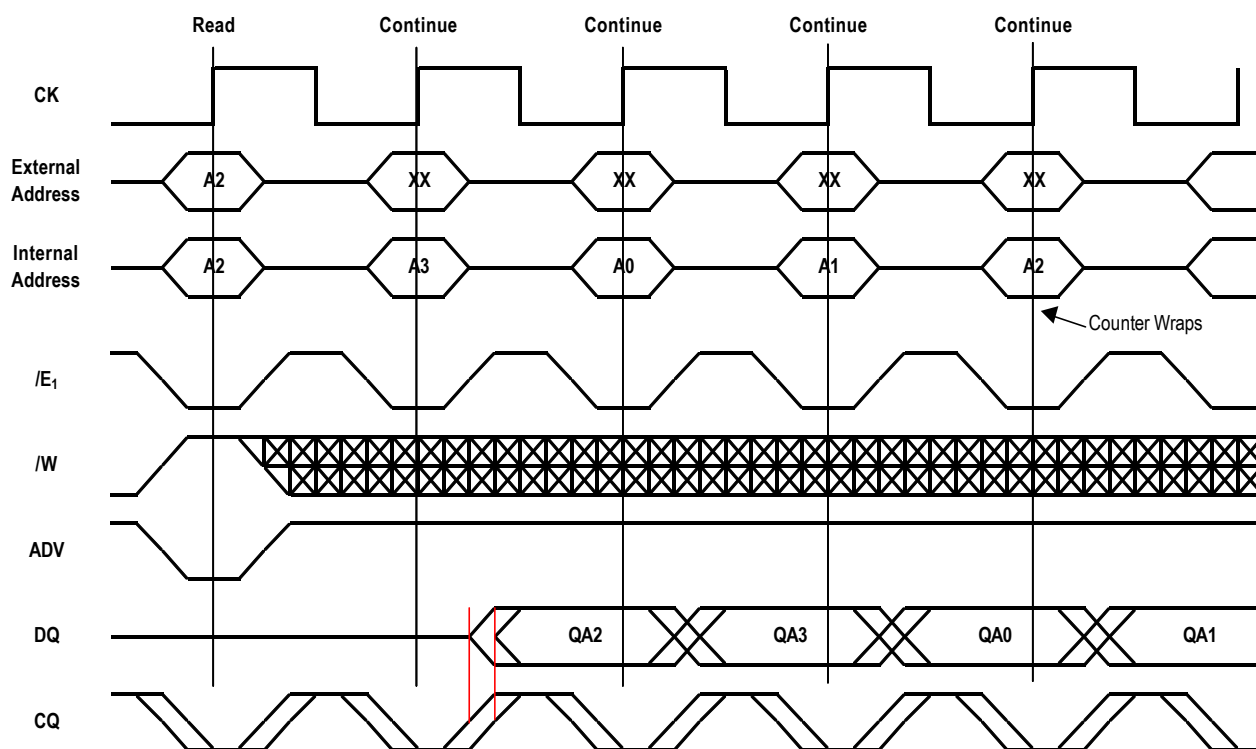
### Slow Down Mode

The  $\overline{SD}$  pin allows the user to activate a delay element in the on-chip clock chain that is routed to the data and echo Clock output drivers. Activating Slow Down mode by pulling the  $\overline{SD}$  pin low introduces extra delay in every synchronous output driver specification. Address, control and data input specifications are not affected by Slow Down Mode. Slow Down Mode has no effect on Flow Through Mode output driver timing. See Table , “Slow Down Mode Clock to Data Out and Clock to Echo Clock Timing,” on page 33 for specifics.

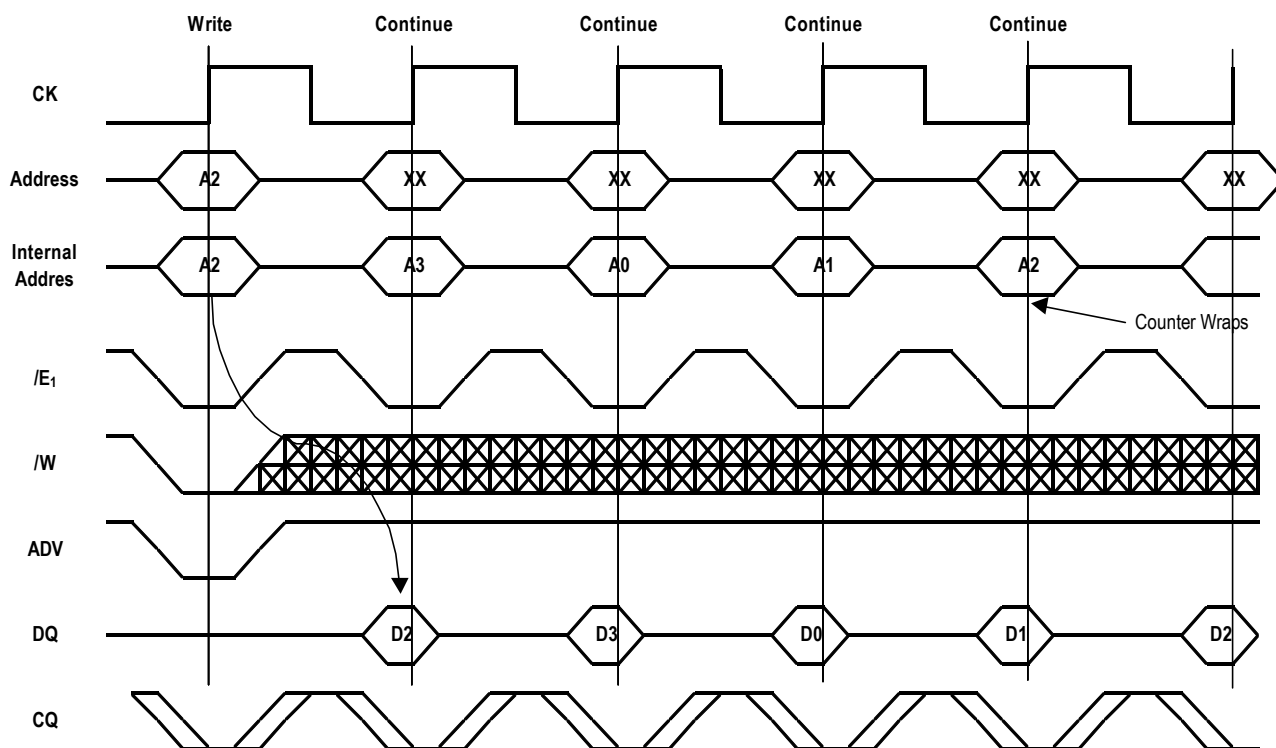
### Burst Cycles

Although  $\Sigma$ RAMs can sustain 100% bus bandwidth by eliminating the bus turnaround cycle in both Late Write Flow through and Double Late Write Pipelined modes, multiple back-to-back reads or writes may also be performed.  $\Sigma$ RAMs provide an on-chip burst address generator that can be utilized, if desired, to further simplify burst read or write implementations. The ADV control pin, when driven high, commands the SRAM to advance the internal address counter and use the counter generated address to read or write the SRAM. The starting address for the first cycle in a burst cycle series is loaded into the SRAM by driving the ADV pin low, into Load mode.

### SigmaRAM Pipelined Burst Reads with Counter Wrap-around



### SigmaRAM Late Write SRAM Burst Writes with Counter Wrap-around



## Burst Order

The burst address counter wraps around to its initial state after four addresses (the loaded address and three more) have been accessed. SigmaRAMs always count in linear burst order.

## Linear Burst Order

	A[1:0]	A[1:0]	A[1:0]	A[1:0]
1st address	00	01	10	11
2nd address	01	10	11	00
3rd address	10	11	00	01
4th address	11	00	01	10

Notes:

1. The burst counter wraps to initial state on the 5th rising edge of clock.

## Echo Clock

$\Sigma$ RAMs feature Echo Clocks, CQ1, CQ2,  $\overline{\text{CQ1}}$ , and  $\overline{\text{CQ2}}$  that track the performance of the output drivers. The Echo Clocks are delayed copies of the main RAM clock, CK. Echo Clocks are designed to track changes in output driver delays due to variance in die temperature and supply voltage. The Echo Clocks are designed to fire with the rest of the data output drivers. SigmaRAMs provide both in-phase, or true, Echo Clock outputs (CQ1 and CQ2) and inverted Echo Clock outputs ( $\overline{\text{CQ1}}$  and  $\overline{\text{CQ2}}$ ).

It should be noted that deselection of the RAM via E2 and E3 also deselects the Echo Clock output drivers. The deselection of Echo Clock drivers is always pipelined to the same degree as output data. **Deselection of the RAM via E1 does not deactivate the Echo Clocks.**

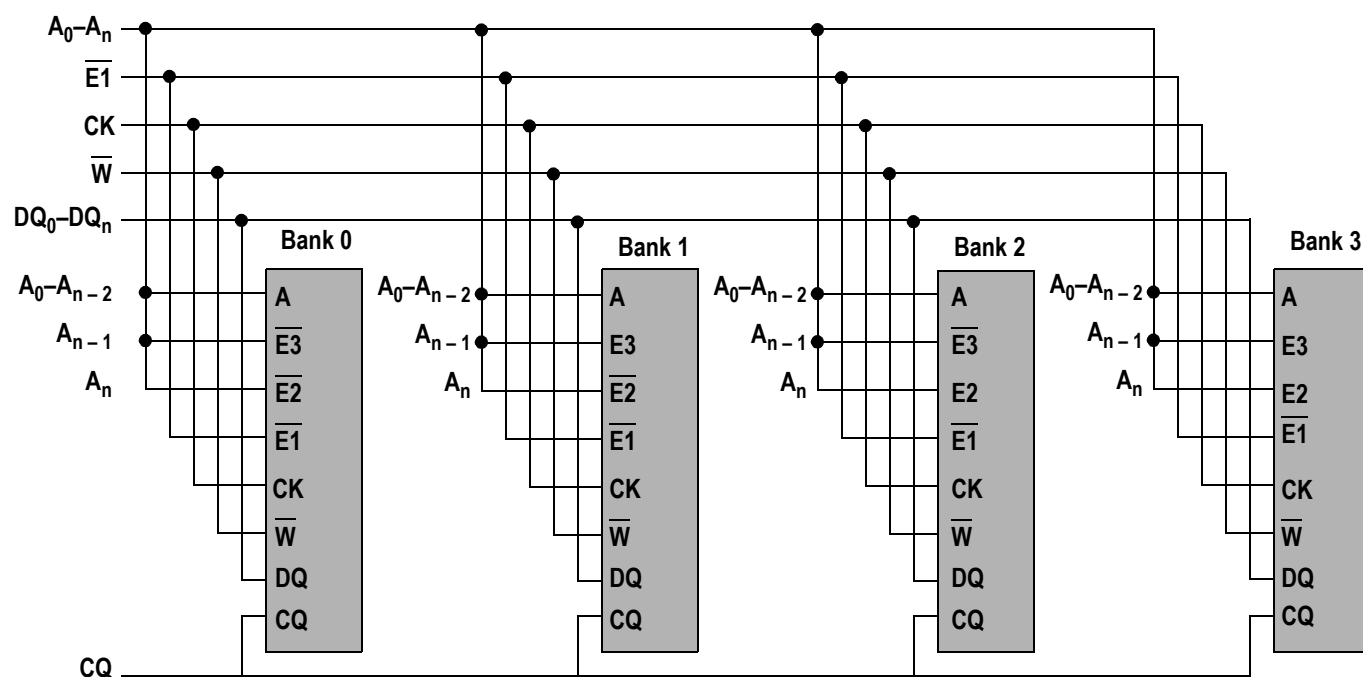
## Programmable Enables

$\Sigma$ RAMs feature two user-programmable chip enable inputs, E2 and E3. The sense of the inputs, whether they function as active low or active high inputs, is determined by the state of the programming inputs, PE2 and PE3. For example, if PE2 is held at  $V_{DD}$ , E2 functions as an active high enable. If PE2 is held to  $V_{SS}$ , E2 functions as an active low chip enable input.

Programmability of E2 and E3 allows four banks of depth expansion to be accomplished with no additional logic. By programming the enable inputs of four  $\Sigma$ RAMs in binary sequence (00, 01, 10, 11) and driving the enable inputs with two address inputs, four  $\Sigma$ RAMs can be made to look like one larger RAM to the system.



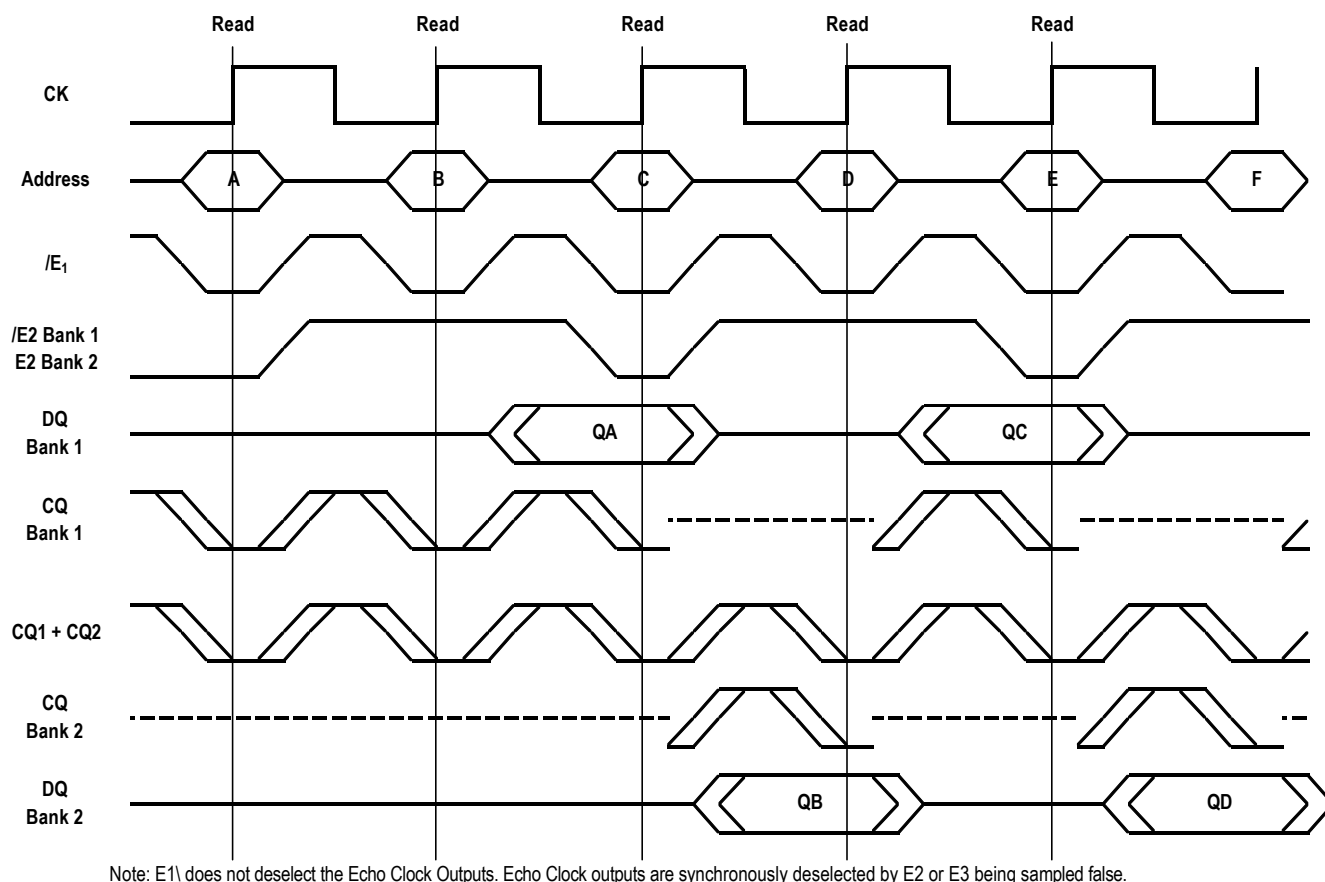
### Example Four Bank Depth Expansion Schematic - $\Sigma 1x1Lp$ and $\Sigma 1x1Dp$



Bank Enable Truth Table

	EP2	EP3	E2	E3
Bank 0	$V_{SS}$	$V_{SS}$	Active Low	Active Low
Bank 1	$V_{SS}$	$V_{DD}$	Active Low	Active High
Bank 2	$V_{DD}$	$V_{SS}$	Active High	Active Low
Bank 3	$V_{DD}$	$V_{DD}$	Active High	Active High

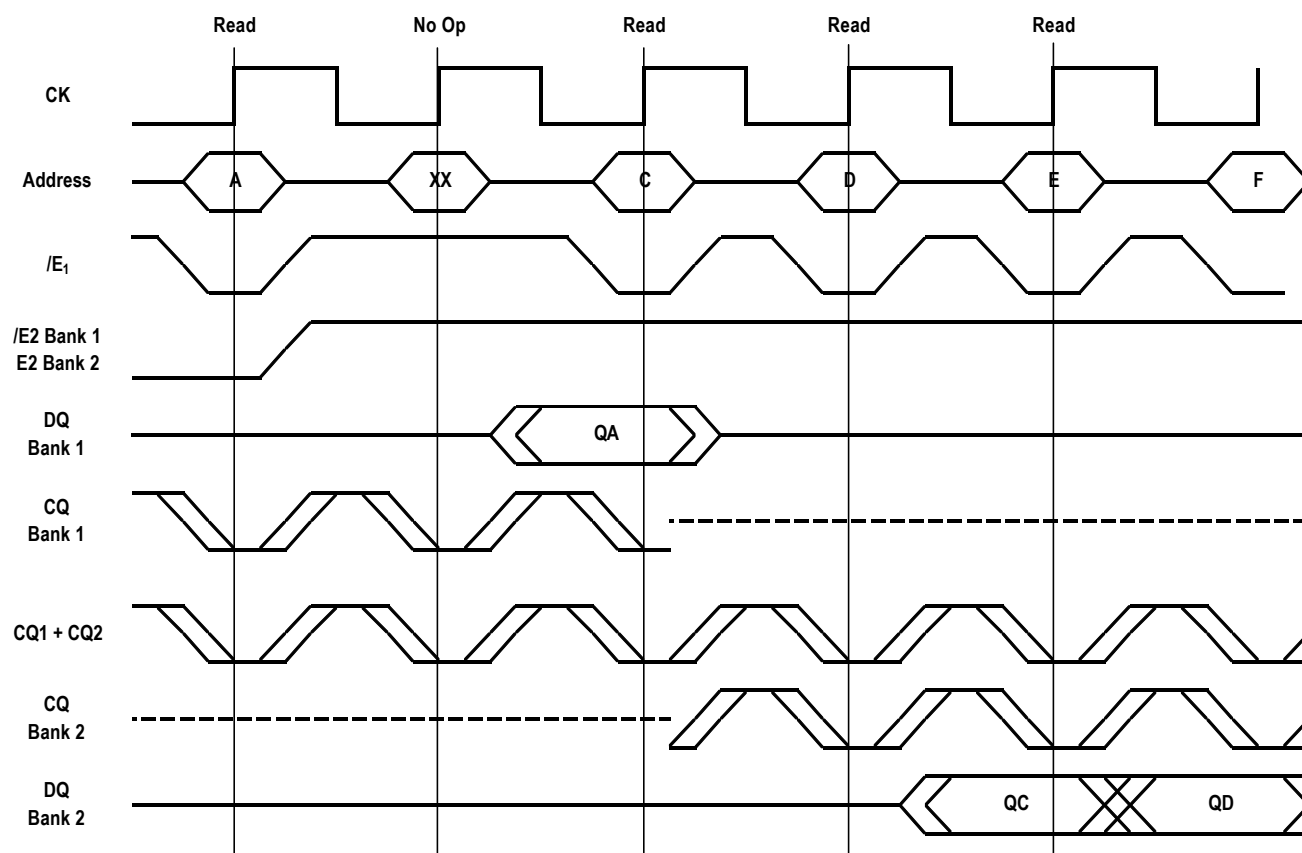
# Echo Clock Control in Two Banks of SigmaRAM Pipelined SRAMs



It should be noted that deselection of the RAM via E2 and E3 also deselects the Echo Clock output drivers. The deselection of Echo Clock drivers is always pipelined to the same degree as output data. Deselection of the RAM via  $\overline{E1}$  does not deactivate the Echo Clocks.

In some applications it may be appropriate to pause between banks; to deselect both RAMs with  $\overline{E1}$  before resuming read operations. An  $\overline{E1}$  deselect at a bank switch will allow at least one clock to be issued from the new bank before the first read cycle in the bank. Although the following drawing illustrates a  $\overline{E1}$  read pause upon switching from Bank 1 to Bank 2, a write to Bank 2 would have the same effect, causing the RAM in Bank 2 to issue at least one clock before it is needed.

### Pipelined Read Bank Switch with $\overline{E1}$ Deselect



Note:  $\overline{E1}$  does not deselect the Echo Clock Outputs. Echo Clock outputs are synchronously deselected by  $\overline{E2}$  or  $\overline{E3}$  being sampled false.

### FLXDrive™ Output Driver Impedance Control

The ZQ pin allows selection between  $\Sigma$ RAM nominal drive strength (ZQ low) for multi-drop bus applications and low drive strength (ZQ floating or high) point-to-point applications. See "Output Driver Characteristics" on page 42 for details.

# 1x1Ef Synchronous Truth Table

CK	$\overline{E1}$ ( $t_n$ )	E ( $t_n$ )	ADV ( $t_n$ )	$\overline{W}$ ( $t_n$ )	$\overline{BW}$ ( $t_n$ )	Previous Operation	Current Operation	DQ ( $t_n$ )
0→1	X	F	0	X	X	X	Bank Deselect	Hi-Z
0→1	X	X	1	X	X	Bank Deselect	Bank Deselect (Continue)	Hi-Z
0→1	1	T	0	X	X	X	Deselect	Hi-Z
0→1	X	X	1	X	X	Deselect	Deselect (Continue)	Hi-Z
0→1	0	T	0	0	T	X	Write Loads new address Stores DQx if BWx = 0	D1 ( $t_n$ )
0→1	0	T	0	0	F	X	Write (Abort) Loads new address No data stored	Hi-Z
0→1	X	X	1	X	T	Write	Write Continue Increments address by 1 Stores DQx if BWx = 0	Dn ( $t_n$ )
0→1	X	X	1	X	F	Write	Write Continue (Abort) Increments address by 1 No data stored	Hi-Z
0→1	0	T	0	1	X	X	Read Loads new address	Q1 ( $t_n$ )
0→1	X	X	1	X	X	Read	Read Continue Increments address by 1	Qn ( $t_{n-1}$ )

## Notes:

1. If  $E2 = EP2$  and  $E3 = EP3$  then  $E = "T"$  else  $E = "F"$ .
2. If one or more  $\overline{BWx} = 0$  then  $BW = "T"$  else  $BW = "F"$ .
3. "1" = input "high"; "0" = input "low"; "X" = input "don't care"; "T" = input "true"; "F" = input "false".
4. "\*\*\*" indicates that the DQ input requirement / output state and CQ output state are determined by the previous operation.
5. DQs are tri-stated in response to Bank Deselect, Chip Deselect, and Write commands, one full cycle after the command is sampled. They are also tri-stated immediately when  $\overline{G}$  is deasserted (high).
6. Up to three (3) Continue operations may be initiated after a Read or Write operation is initiated to burst transfer up to four (4) distinct pieces of data per single external address input. If a fourth (4th) Continue operation is initiated, the internal address wraps back to the initial external (base) address.

# 1x1Ep Synchronous Truth Table

CK	$\overline{E1}$ ( $t_n$ )	E ( $t_n$ )	ADV ( $t_n$ )	$\overline{W}$ ( $t_n$ )	$\overline{BW}$ ( $t_n$ )	Previous Operation	Current Operation	DQ/CQ ( $t_n$ )	DQ/CQ ( $t_{n+1}$ )
0→1	X	F	0	X	X	X	Bank Deselect	***	Hi-Z
0→1	X	X	1	X	X	Bank Deselect	Bank Deselect (Continue)	Hi-Z/Hi-Z	Hi-Z
0→1	1	T	0	X	X	X	Deselect	***	Hi-Z/CQ
0→1	X	X	1	X	X	Deselect	Deselect (Continue)	Hi-Z/CQ	Hi-Z/CQ
0→1	0	T	0	0	T	X	Write Loads new <u>address</u> Stores DQx if BWx = 0	D1/CQ ( $t_n$ )	***
0→1	0	T	0	0	F	X	Write (Abort) Loads new address No data stored	Hi-Z/CQ	***
0→1	X	X	1	X	T	Write	Write Continue Increments <u>address</u> by 1 Stores DQx if BWx = 0	Dn/CQ ( $t_n$ )	Hi-Z/CQ
0→1	X	X	1	X	F	Write	Write Continue (Abort) Increments address by 1 No data stored	Hi-Z/CQ	Hi-Z/CQ
0→1	0	T	0	1	X	X	Read Loads new address	***	Qn/CQ ( $t_n$ )
0→1	X	X	1	X	X	Read	Read Continue Increments address by 1	Qn-1/CQ ( $t_{n-1}$ )	Qn/CQ ( $t_n$ )

## Notes:

1. If E2 = EP2 and E3 = EP3 then E = "T" else E = "F".
2. If one or more  $\overline{BW}x = 0$  then BW = "T" else BW = "F".
3. "1" = input "high"; "0" = input "low"; "X" = input "don't care"; "T" = input "true"; "F" = input "false".
4. "\*\*\*" indicates that the DQ input requirement / output state and CQ output state are determined by the previous operation.
5. DQs are tri-stated in response to Bank Deselect, Chip Deselect, and Write commands, one full cycle after the command is sampled.
6. CQs are tri-stated in response to Bank Deselect commands only, one full cycle after the command is sampled.
7. Up to three (3) Continue operations may be initiated after a Read or Write operation is initiated to burst transfer up to four (4) distinct pieces of data per single external address input. If a fourth (4th) Continue operation is initiated, the internal address wraps back to the initial external (base) address.

# 1x1Lf Synchronous Truth Table

CK	$\overline{E1}$ ( $t_n$ )	E ( $t_n$ )	ADV ( $t_n$ )	$\overline{W}$ ( $t_n$ )	$\overline{BW}$ ( $t_n$ )	Previous Operation	Current Operation	DQ/CQ ( $t_n$ )	DQ/CQ ( $t_{n+1}$ )
0→1	X	F	0	X	X	X	Bank Deselect	Hi-Z	Hi-Z
0→1	X	X	1	X	X	Bank Deselect	Bank Deselect (Continue)	Hi-Z	Hi-Z
0→1	1	T	0	X	X	X	Deselect	Hi-Z	Hi-Z/CQ
0→1	X	X	1	X	X	Deselect	Deselect (Continue)	Hi-Z	Hi-Z/CQ
0→1	0	T	0	0	T	X	Write Loads new <u>address</u> Stores DQx if BWx = 0	***	Dn ( $t_n$ )
0→1	0	T	0	0	F	X	Write (Abort) Loads new address No data stored	***	Hi-Z
0→1	X	X	1	X	T	Write	Write Continue Increments <u>address</u> by 1 Stores DQx if BWx = 0	Dn-1 ( $t_{n-1}$ )	Dn ( $t_n$ )
0→1	X	X	1	X	F	Write	Write Continue (Abort) Increments address by 1 No data stored	Dn-1 ( $t_{n-1}$ )	Hi-Z
0→1	0	T	0	1	X	X	Read Loads new address	Qn ( $t_n$ )	***
0→1	X	X	1	X	X	Read	Read Continue Increments address by 1	Qn ( $t_n$ )	***

## Notes:

1. If E2 = EP2 and E3 = EP3 then E = "T" else E = "F".
2. If one or more  $\overline{BW}x = 0$  then BW = "T" else BW = "F".
3. "1" = input "high"; "0" = input "low"; "X" = input "don't care"; "T" = input "true"; "F" = input "false".
4. "\*\*\*" indicates that the DQ input requirement / output state are determined by the previous or next operation.
5. DQs are tri-stated in response to Bank Deselect, Chip Deselect, and Write commands, one full cycle after the command is sampled.
6. CQs are tri-stated in response to Bank Deselect commands only, one full cycle after the command is sampled.
7. Up to three (3) Continue operations may be initiated after a Read or Write operation is initiated to burst transfer up to four (4) distinct pieces of data per single external address input. If a fourth (4th) Continue operation is initiated, the internal address wraps back to the initial external (base) address.

# 1x1Lp Synchronous Truth Table

CK	$\overline{E1}$ ( $t_n$ )	E ( $t_n$ )	ADV ( $t_n$ )	$\overline{W}$ ( $t_n$ )	$\overline{BW}$ ( $t_n$ )	Previous Operation	Current Operation	DQ/CQ ( $t_n$ )	DQ/CQ ( $t_{n+1}$ )
0→1	X	F	0	X	X	X	Bank Deselect	***	Hi-Z
0→1	X	X	1	X	X	Bank Deselect	Bank Deselect (Continue)	Hi-Z	Hi-Z
0→1	1	T	0	X	X	X	Deselect	***	Hi-Z/CQ
0→1	X	X	1	X	X	Deselect	Deselect (Continue)	Hi-Z/CQ	Hi-Z/CQ
0→1	0	T	0	0	T	X	Write Loads new address Stores DQx if BWx = 0	***	Dn/CQ ( $t_n$ )
0→1	0	T	0	0	F	X	Write (Abort) Loads new address No data stored	***	Hi-Z/CQ
0→1	X	X	1	X	T	Write	Write Continue Increments address by 1 Stores DQx if BWx = 0	Dn-1/CQ ( $t_{n-1}$ )	Dn/CQ ( $t_n$ )
0→1	X	X	1	X	F	Write	Write Continue (Abort) Increments address by 1 No data stored	Dn-1/CQ ( $t_{n-1}$ )	Hi-Z/CQ
0→1	0	T	0	1	X	X	Read Loads new address	***	Qn/CQ ( $t_n$ )
0→1	X	X	1	X	X	Read	Read Continue Increments address by 1	Qn-1/CQ ( $t_{n-1}$ )	Qn/CQ ( $t_n$ )

## Notes:

1. If E2 = EP2 and E3 = EP3 then E = "T" else E = "F".
2. If one or more  $\overline{BW}x = 0$  then BW = "T" else BW = "F".
3. "1" = input "high"; "0" = input "low"; "X" = input "don't care"; "T" = input "true"; "F" = input "false".
4. "\*\*\*" indicates that the DQ input requirement / output state and CQ output state are determined by the previous operation.
5. DQs are tri-stated in response to Bank Deselect, Chip Deselect, and Write commands, one full cycle after the command is sampled.
6. CQs are tri-stated in response to Bank Deselect commands only, one full cycle after the command is sampled.
7. Up to three (3) Continue operations may be initiated after a Read or Write operation is initiated to burst transfer up to four (4) distinct pieces of data per single external address input. If a fourth (4th) Continue operation is initiated, the internal address wraps back to the initial external (base) address.

## 1x1Dp Synchronous Truth Table

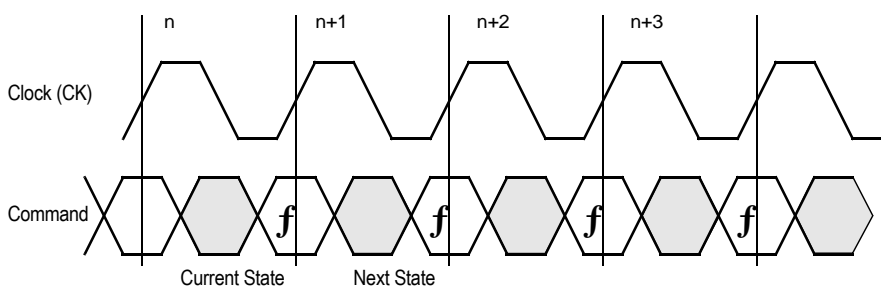
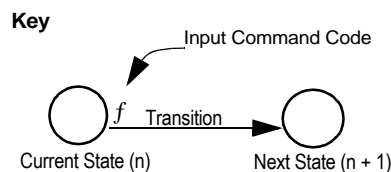
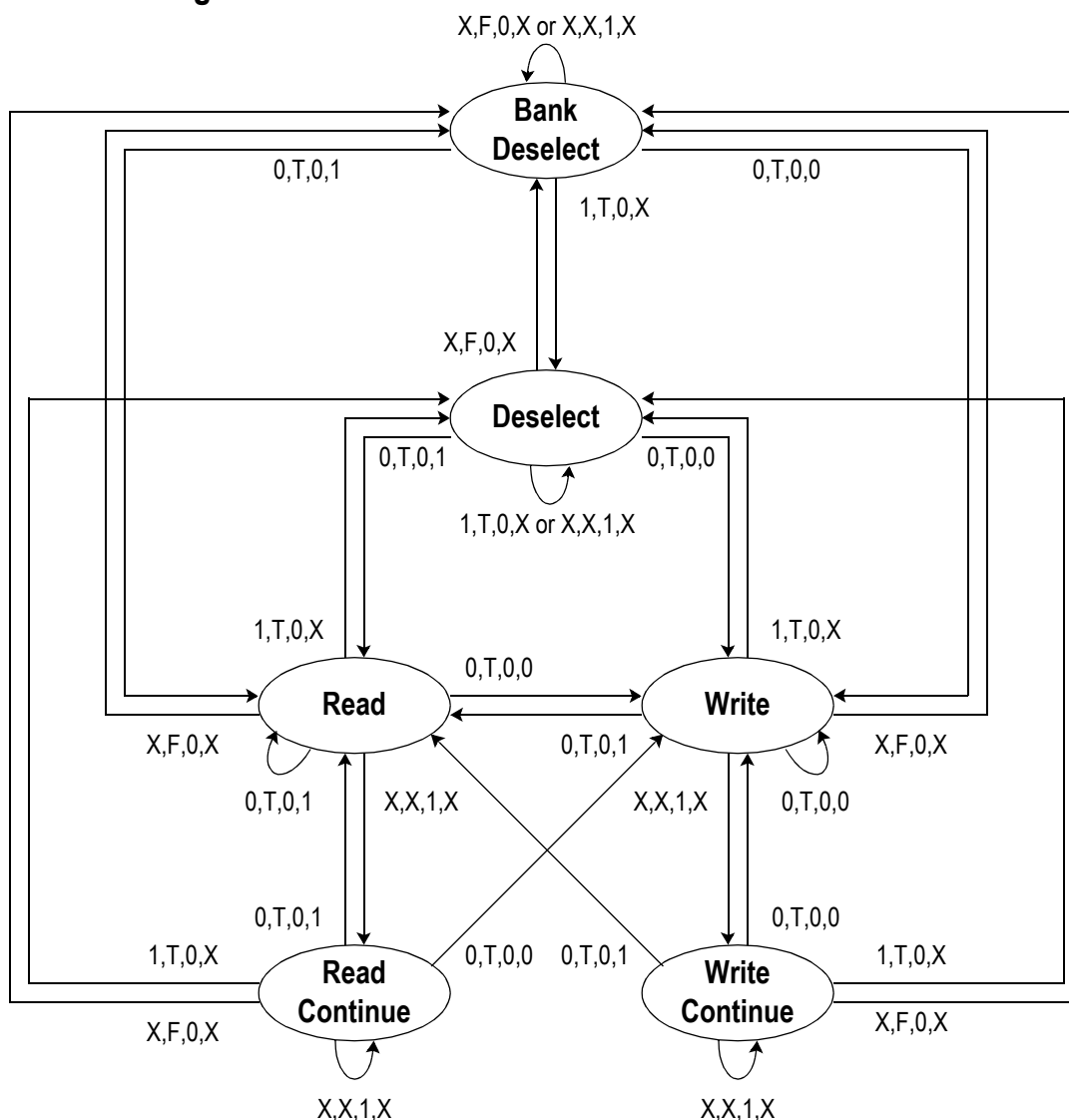
CK	$\overline{E1}$ ( $t_n$ )	E ( $t_n$ )	ADV ( $t_n$ )	$\overline{W}$ ( $t_n$ )	$\overline{BW}$ ( $t_n$ )	Previous Operation	Current Operation	DQ/CQ ( $t_n$ )	DQ/CQ ( $t_{n+1}$ )	DQ/CQ ( $t_{n+2}$ )
0→1	X	F	0	X	X	X	Bank Deselect	***	Hi-Z	---
0→1	X	X	1	X	X	Bank Deselect	Bank Deselect (Continue)	Hi-Z	Hi-Z	---
0→1	1	T	0	X	X	X	Deselect	***	Hi-Z/CQ	---
0→1	X	X	1	X	X	Deselect	Deselect (Continue)	Hi-Z/CQ	Hi-Z/CQ	---
0→1	0	T	0	0	T	X	Write Loads new address Stores DQx if BWx = 0	***	***	Dn/CQ ( $t_n$ )
0→1	0	T	0	0	F	X	Write (Abort) Loads new address No data stored	***	***	Hi-Z/CQ
0→1	X	X	1	X	T	Write	Write Continue Increments address by 1 Stores DQx if BWx = 0	***	Dn-1/CQ ( $t_{n-1}$ )	Dn/CQ ( $t_n$ )
0→1	X	X	1	X	F	Write	Write Continue (Abort) Increments address by 1 No data stored	***	Dn-1/CQ ( $t_{n-1}$ )	Hi-Z/CQ
0→1	0	T	0	1	X	X	Read Loads new address	***	Qn/CQ ( $t_n$ )	---
0→1	X	X	1	X	X	Read	Read Continue Increments address by 1	Qn-1/CQ ( $t_{n-1}$ )	Qn/CQ ( $t_n$ )	---

### Notes:

1. If E2 = EP2 and E3 = EP3 then E = "T" else E = "F".
2. If one or more  $\overline{BWx} = 0$  then BW = "T" else BW = "F".
3. "1" = input "high"; "0" = input "low"; "X" = input "don't care"; "T" = input "true"; "F" = input "false".
4. "\*\*\*" indicates that the DQ input requirement / output state and CQ output state are determined by the previous operation.
5. "---" indicates that the DQ input requirement / output state and CQ output state are determined by the next operation.
6. DQs are tri-stated in response to Bank Deselect, Chip Deselect, and Write commands, one full cycle after the command is sampled.
7. CQs are tri-stated in response to Bank Deselect commands only, one full cycle after the command is sampled.
8. Up to three (3) Continue operations may be initiated after a Read or Write operation is initiated to burst transfer up to four (4) distinct pieces of data per single external address input. If a fourth (4th) Continue operation is initiated, the internal address wraps back to the initial external (base) address.



## Common I/O State Diagram



### Current State & Next State Definition for Read/Write Control State Diagram

Notes:

1. The notation “X,X,X,X” controlling the state transitions above indicate the states of inputs  $\overline{E1}$ , E, ADV, and  $\overline{W}$  respectively.
2. If (E2 = EP2 and E3 = EP3) then E = “T” else E = “F”.
3. “1” = input “high”; “0” = input “low”; “X” = input “don’t care”; “T” = input “true”; “F” = input “false”.

## Absolute Maximum Ratings

(All voltages reference to  $V_{SS}$ )

Symbol	Description	Value	Unit
$V_{DD}$	Voltage on $V_{DD}$ Pins	-0.5 to 2.5	V
$V_{DDQ}$	Voltage in $V_{DDQ}$ Pins	-0.5 to $V_{DD}$	V
$V_{I/O}$	Voltage on I/O Pins	-0.5 to $V_{DDQ}+0.5$ ( $\leq 2.5$ V max.)	V
$V_{IN}$	Voltage on Other Input Pins	-0.5 to $V_{DDQ}+0.5$ ( $\leq 2.5$ V max.)	V
$I_{IN}$	Input Current on Any Pin	+/-100	mA dc
$I_{OUT}$	Output Current on Any I/O Pin	+/-100	mA dc
$T_J$	Maximum Junction Temperature	125	°C
$T_{STG}$	Storage Temperature	-55 to 125	°C

Note:

Permanent damage to the device may occur if the Absolute Maximum Ratings are exceeded. Operation should be restricted to Recommended Operating Conditions. Exposure to conditions exceeding the Recommended Operating Conditions, for an extended period of time, may affect reliability of this component.

## Recommended Operating Conditions

### Power Supplies

Parameter	Symbol	Min.	Typ.	Max.	Unit	Notes
Supply Voltage	$V_{DD}$	1.7	1.8	1.95	V	
1.8 V I/O Supply Voltage	$V_{DDQ}$	1.7	1.8	$V_{DD}$	V	1
1.5 V I/O Supply Voltage	$V_{DDQ}$	1.4	1.5	1.6 V	V	1
Ambient Temperature (Commercial Range Versions)	$T_A$	0	25	70	°C	2
Ambient Temperature (Industrial Range Versions)	$T_A$	-40	25	85	°C	2

Notes:

1. Unless otherwise noted, all performance specifications quoted are evaluated for worst case at both  $1.4\text{ V} \leq V_{DDQ} \leq 1.6\text{ V}$  (i.e., 1.5 V I/O) and  $1.7\text{ V} \leq V_{DDQ} \leq 1.95\text{ V}$  (i.e., 1.8 V I/O) and quoted at whichever condition is worst case.
2. Most speed grades and configurations of this device are offered in both Commercial and Industrial Temperature ranges. The part number of Industrial Temperature Range versions end the character "I". Unless otherwise noted, all performance specifications quoted are evaluated for worst case in the temperature range marked on the device.

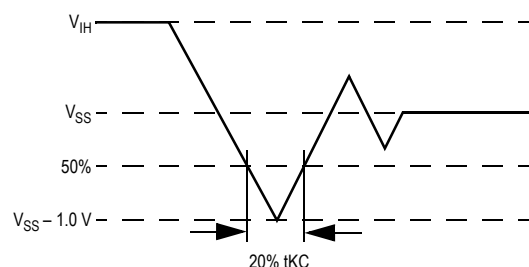
## CMOS I/O DC Input Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Notes
CMOS Input High Voltage	$V_{IH}$	$0.65 * V_{DDQ}$	—	$V_{DD} + 0.3$	V	1
CMOS Input Low Voltage	$V_{IL}$	-0.3	—	$0.35 * V_{DDQ}$	V	1

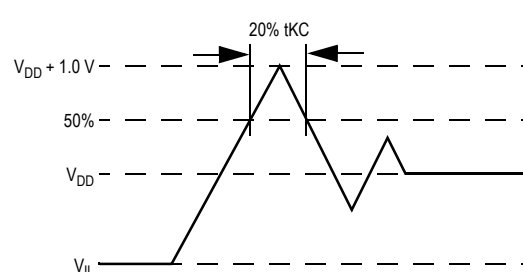
Note:

- For devices supplied with CMOS input buffers. Compatible with both 1.8 V and 1.5 V I/O drivers.

## Undershoot Measurement and Timing



## Overshoot Measurement and Timing



## Capacitance

( $T_A = 25^\circ\text{C}$ ,  $f = 1\text{ MHz}$ ,  $V_{DD} = 3.3\text{ V}$ )

Parameter	Symbol	Test conditions	Typ.	Max.	Unit
Input Capacitance	$C_{IN}$	$V_{IN} = 0\text{ V}$	4	5	pF
Output Capacitance	$C_{OUT}$	$V_{OUT} = 0\text{ V}$	6	7	pF

Note: This parameter is sample tested.

## Package Thermal Characteristics

Rating	Layer Board	Symbol	Max	Unit	Notes
Junction to Ambient (at 200 lfm)	single	$R_{\Theta JA}$	TBD	$^\circ\text{C/W}$	1,2
Junction to Ambient (at 200 lfm)	four	$R_{\Theta JA}$	TBD	$^\circ\text{C/W}$	1,2
Junction to Case (TOP)	n/a	$R_{\Theta JC}$	TBD	$^\circ\text{C/W}$	3

Notes:

- Junction temperature is a function of SRAM power dissipation, package thermal resistance, mounting board temperature, ambient. Temperature air flow, board density, and PCB thermal resistance.
- SCMI G-38-87
- Average thermal resistance between die and top surface, MIL SPEC-883, Method 1012.1

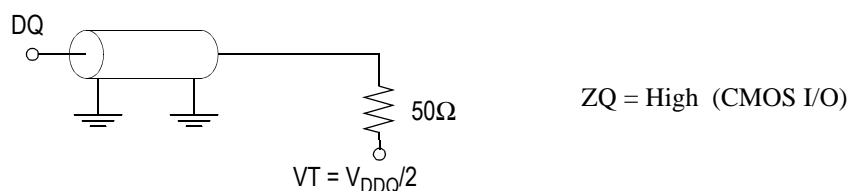
## AC Test Conditions

Parameter	Conditions
Input high level	$V_{DDQ}$
Input low level	0 V
Max. input slew rate	2 V/ns
Input reference level	$V_{DDQ}/2$
Output reference level	$V_{DDQ}/2$

### Notes:

1. Include scope and jig capacitance.
2. Test conditions as specified with output loading as shown unless otherwise noted.

## AC Test Load Diagram



## Input and Output Leakage Characteristics

Parameter	Symbol	Test Conditions	Min.	Max	Notes
Input Leakage Current (except mode pins)	$I_{IL}$	$V_{IN} = 0 \text{ to } V_{DD}$	-2 $\mu$ A	2 $\mu$ A	—
Mode Pin Input Current	$I_{INM}$	$V_{DD} \geq V_{IN} \geq V_{IL}$ $0V \leq V_{IN} \leq V_{IL}$	-100 $\mu$ A -2 $\mu$ A	2 $\mu$ A 2 $\mu$ A	—
Output Leakage Current	$I_{OL}$	Output Disable, $V_{OUT} = 0 \text{ to } V_{DDQ}$	-2 $\mu$ A	2 $\mu$ A	—

## Selectable Impedance Output Driver DC Electrical Characteristics

Parameter	Symbol	Test Conditions	Min.	Max	Notes
Low Drive Output High Voltage	$V_{OHL}$	$I_{OHL} = -4 \text{ mA}$	$V_{DDQ} - 0.4 \text{ V}$	—	1
Low Drive Output Low Voltage	$V_{OLL}$	$I_{OLL} = 4 \text{ mA}$	—	0.4 V	1
High Drive Output High Voltage	$V_{OHH}$	$I_{OHH} = -8 \text{ mA}$	$V_{DDQ} - 0.4 \text{ V}$	—	2
High Drive Output Low Voltage	$V_{OLH}$	$I_{OLH} = 8 \text{ mA}$	—	0.4 V	2

Notes:

1.  $ZQ = 1$ ; High Impedance output driver setting
2.  $ZQ = 0$ ; Low Impedance output driver setting

# Operating Currents

Parameter		Symbol	-333		-300		-250		Test Conditions
			0°C to 70°C	-40°C to +85°C	0°C to 70°C	-40°C to +85°C	0°C to 70°C	-40°C to +85°C	
Operating Current	x72	I <sub>DDP</sub> Pipeline	650 mA	TBD mA	600 mA	TBD mA	525 mA	TBD mA	$\overline{E1} \leq V_{IL}$ Max. $t_{KHKH} \geq t_{KHKH}$ Min. All other inputs $V_{IL} \geq V_{IN} \geq V_{IH}$
		I <sub>DDF</sub> Flow-through	TBD mA	TBD mA	TBD mA	TBD mA	TBD mA	TBD mA	
	x36	I <sub>DDP</sub> Pipeline	475 mA	TBD mA	445 mA	TBD mA	395 mA	TBD mA	
		I <sub>DDF</sub> Flow-through	TBD mA	TBD mA	TBD mA	TBD mA	TBD mA	TBD mA	
	x18	I <sub>DDP</sub> Pipeline	360 mA	TBD mA	340 mA	TBD mA	310 mA	TBD mA	
		I <sub>DDF</sub> Flow-through	TBD mA	TBD mA	TBD mA	TBD mA	TBD mA	TBD mA	
Chip Disable Current	x72	I <sub>SB1</sub> Pipeline	250 mA	TBD mA	240 mA	TBD mA	225 mA	TBD mA	$\overline{E1} \geq V_{IH}$ Min. or $t_{KHKH} \geq t_{KHKH}$ Min. All other inputs $V_{IL} \geq V_{IN} \geq V_{IH}$
		I <sub>SB1</sub> Flow-through	TBD mA	TBD mA	TBD mA	TBD mA	TBD mA	TBD mA	
	x36	I <sub>SB1</sub> Pipeline	215 mA	TBD mA	210 mA	TBD mA	200 mA	TBD mA	
		I <sub>SB1</sub> Flow-through	TBD mA	TBD mA	TBD mA	TBD mA	TBD mA	TBD mA	
Bank Deselect Current	x72	I <sub>SB2</sub> Pipeline	250 mA	TBD mA	240 mA	TBD mA	225 mA	TBD mA	E2 or E3 False $t_{KHKH} \geq t_{KHKH}$ Min. All other inputs $V_{IL} \geq V_{IN} \geq V_{IH}$
		I <sub>SB2</sub> Flow-through	TBD mA	TBD mA	TBD mA	TBD mA	TBD mA	TBD mA	
	x36	I <sub>SB2</sub> Pipeline	215 mA	TBD mA	210 mA	TBD mA	200 mA	TBD mA	
		I <sub>SB2</sub> Flow-through	TBD mA	TBD mA	TBD mA	TBD mA	TBD mA	TBD mA	
	x18	I <sub>SB2</sub> Pipeline	195 mA	TBD mA	190 mA	TBD mA	185 mA	TBD mA	
		I <sub>SB2</sub> Flow-through	TBD mA	TBD mA	TBD mA	TBD mA	TBD mA	TBD mA	
CMOS Deselect Current		I <sub>DD3</sub>	150 mA						Device Deselected All inputs $V_{SS} + 0.10 V$ $\geq V_{IN} \geq$ $V_{DD} - 0.10 V$

## AC Electrical Characteristics

Parameter	Symbol	-333		-300		-250		Unit	Notes
		Min	Max	Min	Max	Min	Max		
Clock Cycle Time	tKHKH	3.0	—	3.3	—	4.0	—	ns	—
Clock High Time	tKHKL	1.2	—	1.3	—	1.5	—	ns	—
Clock Low Time	tKLKH	1.2	—	1.3	—	1.5	—	ns	—
Clock High to Echo Clock Low-Z	tKHCX1	0.5	—	0.5	—	0.5	—	ns	2
Clock High to Echo Clock High	tKHCH	0.5	1.5	0.5	1.7	0.5	2.0	ns	—
Echo Clock High Time	tCHCL	tKHKL +/- 200 ps				tKHKL +/- 250 ps		ns	2
Clock Low to Echo Clock Low	tKLCL	0.5	1.5	0.5	1.7	0.5	2.0	ns	
Echo Clock Low Time	tCLCH	tKHKL +/- 200 ps				tKHKL +/- 250 ps		ns	2
Clock High to Echo Clock High-Z	tKHCZ	0.5	1.5	0.5	1.7	0.5	2.0	ns	1, 2
Clock High to Output in Low-Z	tKHQX1	0.5	—	0.5	—	0.5	—	ns	1
Clock High to Output Valid	tKHQV		1.6		1.8		2.1	ns	—
Clock High to Output Invalid	tKHQX	0.5	—	0.5	—	0.5	—	ns	—
Clock High to Output in High-Z	tKHQZ	0.5	1.6	0.5	1.8	0.5	2.1	ns	1
Echo Clock High to Output Valid	tCHQV	—	0.4	—	0.4	—	0.5	ns	2
Echo Clock High to Output Invalid	tCHQX	-0.4	—	-0.4	—	-0.5	—	ns	2
Flow Thorough Clock Cycle Time	tKHKH	5.0	—	5.5	—	6.7	—	ns	—
Flow Thorough Clock High to Output Valid	tKHQV		5.0	—	5.5	—	6.7	ns	—
Flow Thorough Clock High to Output in High-Z	tKHQZ	1.0	5.0	1.0	5.5	1.0	6.7	ns	1
Flow Thorough Clock High to Output Invalid	tKHQX	1.0	—	1.0	—	1.0	—	ns	—
Flow Thorough Clock High to Output in Low-Z	tKHQX1	0.5	—	0.5	—	0.5	—	ns	1
Address Valid to Clock High	tAVKH	0.6	—	0.7	—	0.8	—	ns	—
Clock High to Address Don't Care	tKHAX	0.4	—	0.4	—	0.5	—	ns	—
Enable Valid to Clock High	tEVKH	0.6	—	0.7	—	0.8	—	ns	—
Clock High to Enable Don't Care	tKHEX	0.4	—	0.4	—	0.5	—	ns	—
Write Valid to Clock High	tWVKH	0.6	—	0.7	—	0.8	—	ns	—
Clock High to Write Don't Care	tKHWX	0.4	—	0.4	—	0.5	—	ns	—
Byte Write Valid to Clock High	tBVKH	0.6	—	0.7	—	0.8	—	ns	—

### Notes:

1. Measured at 100 mV from steady state. Not 100% tested.
2. Guaranteed by design. Not 100% tested.
3. For any specific temperature and voltage tKHCZ < tKHCX1.

Parameter	Symbol	-333		-300		-250		Unit	Notes
		Min	Max	Min	Max	Min	Max		
Clock High to Byte Write Don't Care	tKHBX	0.4	—	0.4	—	0.5	—	ns	—
Data In Valid to Clock High	tDVKH	0.6	—	0.7	—	0.8	—	ns	—
Clock High to Data In Don't Care	tKHDX	0.4	—	0.4	—	0.5	—	ns	—
ADV Valid to Clock High	tadvVKH	0.6	—	0.7	—	0.8	—	ns	—
Clock High to ADV Don't Care	tKHadvX	0.4	—	0.4	—	0.5	—	ns	—

**Notes:**

1. Measured at 100 mV from steady state. Not 100% tested.
2. Guaranteed by design. Not 100% tested.
3. For any specific temperature and voltage tKHCZ < tKHCX1.



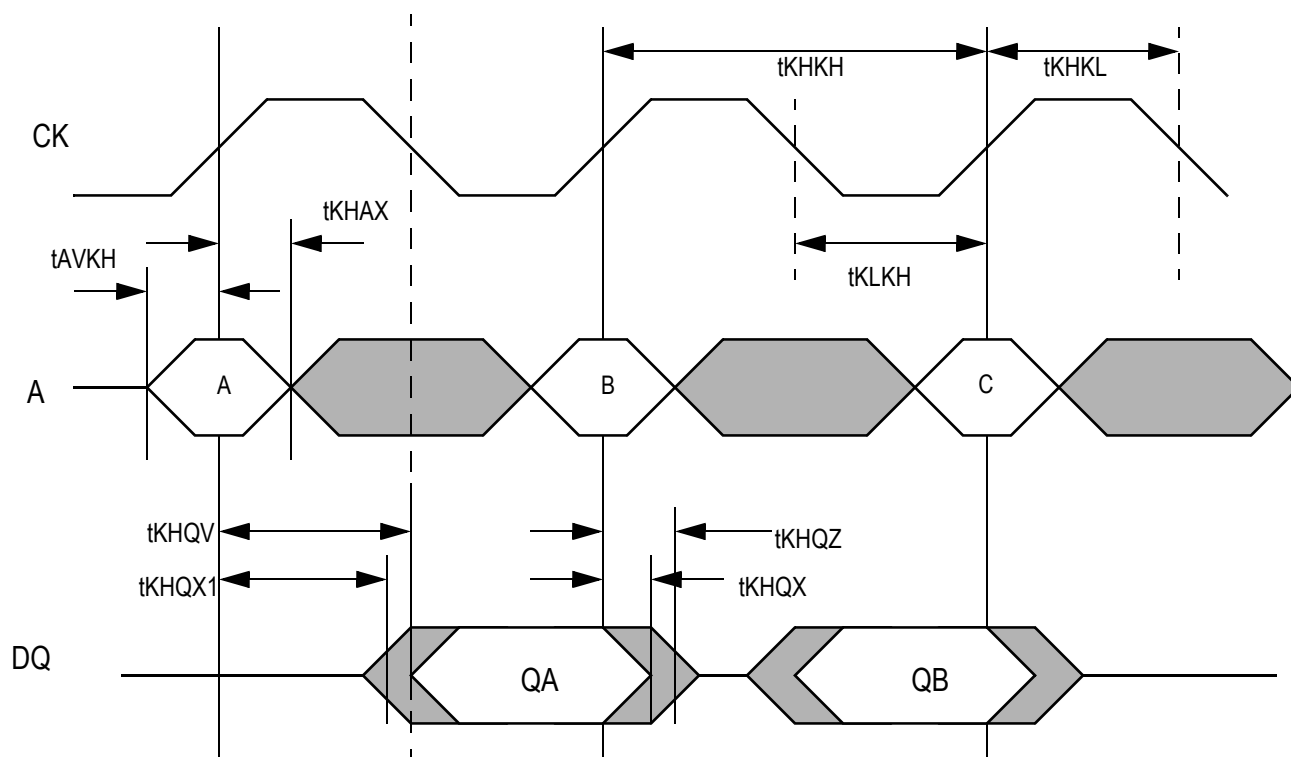
### Slow Down Mode Clock to Data Out and Clock to Echo Clock Timing

Parameter	Symbol	-333		-300		-250		Unit	Notes
		Min	Max	Min	Max	Min	Max		
Clock High to Echo Clock Low-Z	tKHCX1	1.1	—	1.1	—	1.1	—	ns	2
Clock High to Echo Clock High	tKHCH	1.1	2.4	1.1	2.6	1.1	3.1	ns	—
Echo Clock High Time	tCHCL	tKHKL +/- 300 ps				tKHKL +/- 350 ps		ns	2
Echo Clock Low Time	tCLCH	tKHKL +/- 300 ps				tKHKL +/- 350 ps		ns	2
Clock High to Echo Clock High-Z	tKHCZ	1.1	2.4	1.1	2.6	1.1	3.1	ns	1, 2
Clock High to Output in Low-Z	tKHQX1	1.1	—	1.1	—	1.1	—	ns	1
Clock High to Output Valid	tKHQV		2.5		2.7		3.2	ns	—
Clock High to Output Invalid	tKHQX	1.1	—	1.1	—	1.1	—	ns	—
Clock High to Output in High-Z	tKHQZ	1.1	2.5	1.1	2.7	1.1	3.2	ns	1
Echo Clock High to Output Valid	tCHQV	—	0.5	—	0.5	—	0.6	ns	2
Echo Clock High to Output Invalid	tCHQX	—	-0.5	—	-0.5	—	-0.6	ns	2

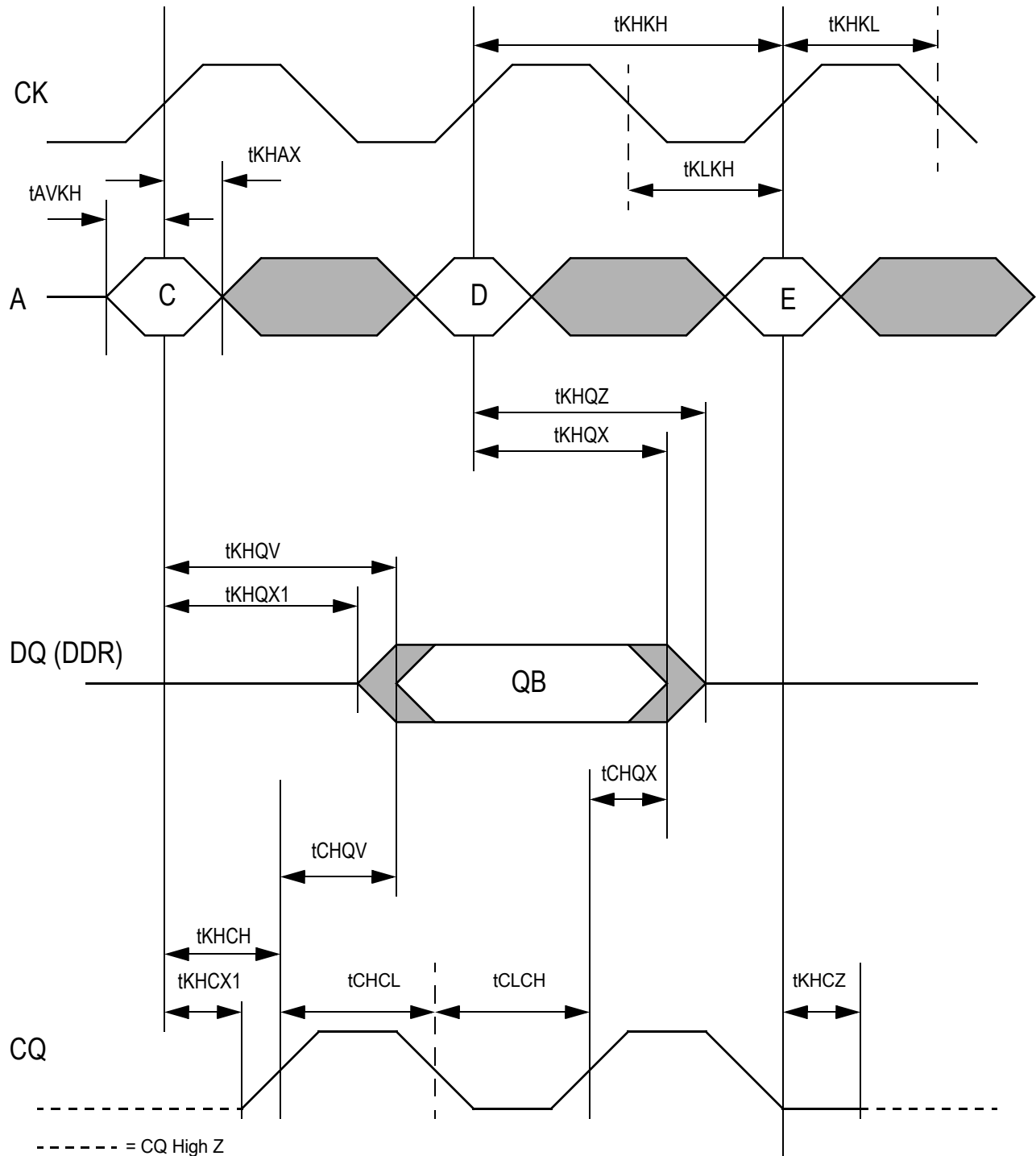
#### Notes:

1. Measured at 100 mV from steady state. Not 100% tested.
2. Guaranteed by design. Not 100% tested.
3. For any specific temperature and voltage tKHCZ < tKHCX1.

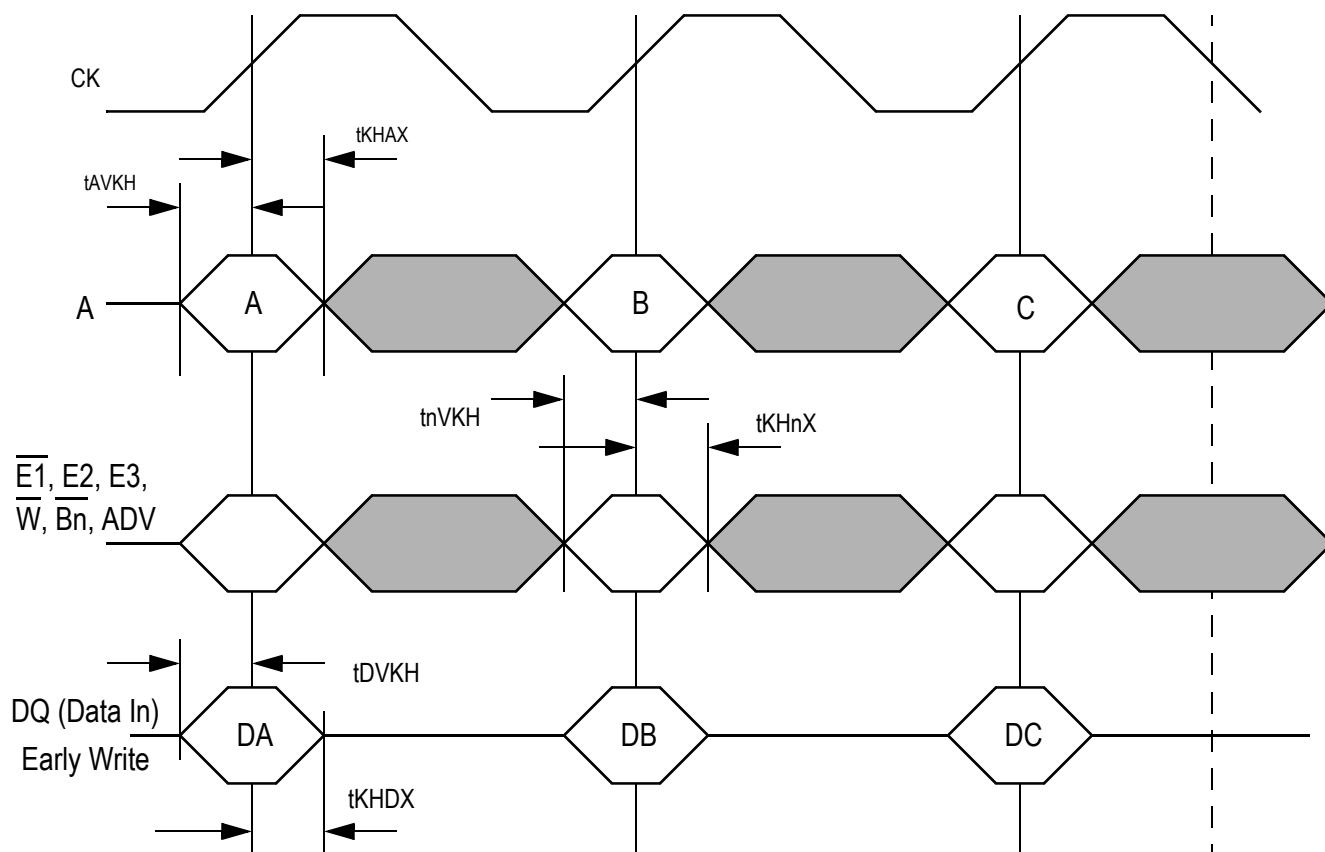
## Timing Parameter Key—Flow Through Read Cycle Timing



## Timing Parameter Key—Pipelined Read Cycle Timing

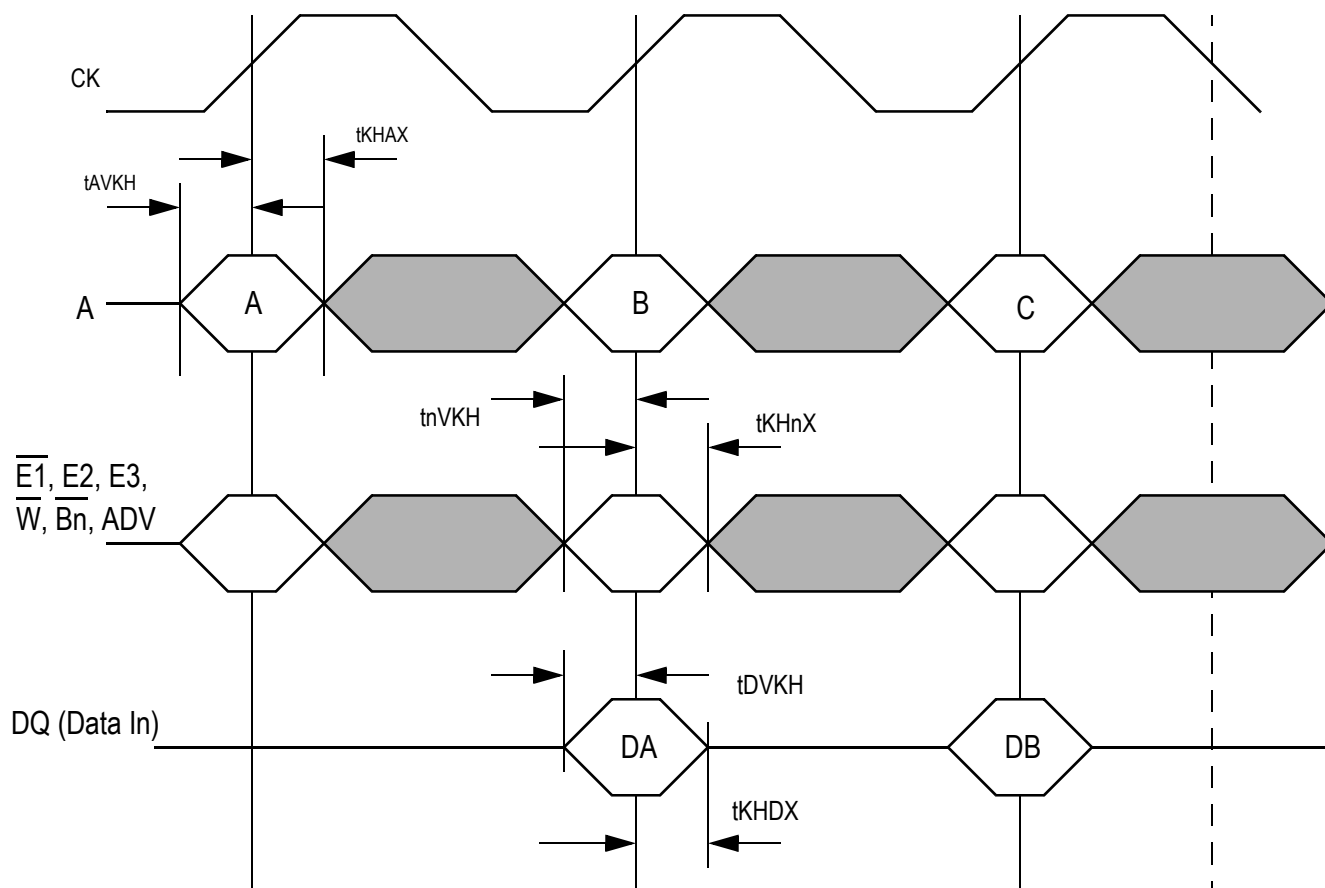


# Timing Parameter Key—Early Write Mode Control and Data In Timing



Note:  $t_{nVKH} = t_{EVKH}, t_{WVKH}, t_{BVKH}$ , etc. and  $t_{KHnX} = t_{KHEX}, t_{KHWX}, t_{KHBX}$ , etc.

## Timing Parameter Key—Late Write Mode Control and Data In Timing



Note:  $t_{nVKH} = t_{EVKH}, t_{WVKH}, t_{BVKH}$ , etc. and  $t_{KHnX} = t_{KHEX}, t_{KHWX}, t_{KHBX}$ , etc.

## JTAG Port Operation

### Overview

The JTAG Port on this RAM operates in a manner that is compliant with IEEE Standard 1149.1-1990, a serial boundary scan interface standard (commonly referred to as JTAG). The JTAG Port input interface levels scale with  $V_{DD}$ . The JTAG output drivers are powered by  $V_{DDQ}$ .

### Disabling the JTAG Port

It is possible to use this device without utilizing the JTAG port. The port is reset at power-up and will remain inactive unless clocked. To assure normal operation of the RAM with the JTAG Port unused, TCK, TDI, and TMS may be left floating or tied to  $V_{DD}$ . TDO should be left unconnected.

## JTAG Pin Descriptions

Pin	Pin Name	I/O	Description
TCK	Test Clock	In	Clocks all TAP events. All inputs are captured on the rising edge of TCK and all outputs propagate from the falling edge of TCK.
TMS	Test Mode Select	In	The TMS input is sampled on the rising edge of TCK. This is the command input for the TAP controller state machine. An undriven TMS input will produce the same result as a logic one input level.
TDI	Test Data In	In	The TDI input is sampled on the rising edge of TCK. This is the input side of the serial registers placed between TDI and TDO. The register placed between TDI and TDO is determined by the state of the TAP Controller state machine and the instruction that is currently loaded in the TAP Instruction Register (refer to the TAP Controller State Diagram). An undriven TDI pin will produce the same result as a logic one input level.
TDO	Test Data Out	Out	Output that is active depending on the state of the TAP state machine. Output changes in response to the falling edge of TCK. This is the output side of the serial registers placed between TDI and TDO.

Note:

This device does not have a TRST (TAP Reset) pin. TRST is optional in IEEE 1149.1. The Test-Logic-Reset state is entered while TMS is held high for five rising edges of TCK. The TAP Controller is also reset automatically at power-up.

## JTAG Port Registers

### Overview

The various JTAG registers, referred to as Test Access Port or TAP Registers, are selected (one at a time) via the sequences of 1s and 0s applied to TMS as TCK is strobed. Each of the TAP registers are serial shift registers that capture serial input data on the rising edge of TCK and push serial data out on the next falling edge of TCK. When a register is selected, it is placed between the TDI and TDO pins.

### Instruction Register

The Instruction Register holds the instructions that are executed by the TAP controller when it is moved into the Run, Test/Idle, or the various data register states. Instructions are 3 bits long. The Instruction Register can be loaded when it is placed between the TDI and TDO pins. The Instruction Register is automatically preloaded with the IDCODE instruction at power-up or whenever the controller is placed in Test-Logic-Reset state.

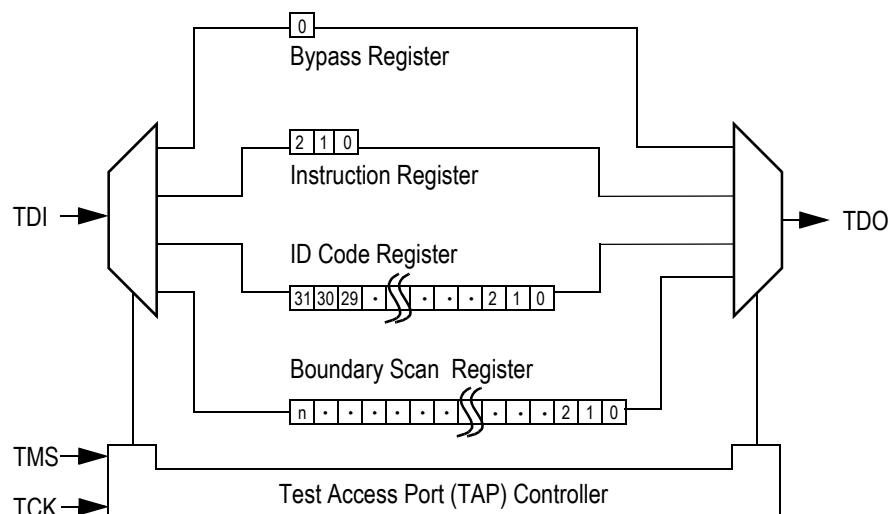
### Bypass Register

The Bypass Register is a single-bit register that can be placed between TDI and TDO. It allows serial test data to be passed through the RAM's JTAG Port to another device in the scan chain with as little delay as possible.

### Boundary Scan Register

The Boundary Scan Register is a collection of flip flops that can be preset by the logic level found on the RAM's input or I/O pins. The flip flops are then daisy chained together so the levels found can be shifted serially out of the JTAG Port's TDO pin. The Boundary Scan Register also includes a number of place holder flip flops (always set to a logic 1). The relationship between the device pins and the bits in the Boundary Scan Register is described in the Scan Order Table following. The Boundary Scan Register, under the control of the TAP Controller, is loaded with the contents of the RAMs I/O ring when the controller is in Capture-DR state and then is placed between the TDI and TDO pins when the controller is moved to Shift-DR state. SAMPLE-Z, SAMPLE/PRELOAD and EXTEST instructions can be used to activate the Boundary Scan Register.

## JTAG TAP Block Diagram



### Identification (ID) Register

The ID Register is a 32-bit register that is loaded with a device and vendor specific 32-bit code when the controller is put in Capture-DR state with the IDCODE command loaded in the Instruction Register. The code is loaded from a 32-bit on-chip ROM. It describes various attributes of the RAM as indicated below. The register is then placed between the TDI and TDO pins when the controller is moved into Shift-DR state. Bit 0 in the register is the LSB and the first to reach TDO when shifting begins.

## ID Register Contents

	Die Revision Code				Not Used												I/O Configuration				GSI Technology JEDEC Vendor ID Code												Presence Register
Bit #	3 1	3 0	2 9	2 8	2 7	2 6	2 5	2 4	2 3	2 2	2 1	2 0	1 9	1 8	1 7	1 6	1 5	1 4	1 3	1 2	1 1	1 0	9	8	7	6	5	4	3	2	1	0	
x36	X	X	X	X	0	0	0	0	0	0	0	0	0	0	0	0	1	0	0	0	0	0	0	0	1	1	0	1	1	0	0	1	1
x18	X	X	X	X	0	0	0	0	0	0	0	0	0	0	0	0	1	0	1	0	0	0	0	0	1	1	0	1	1	0	0	1	1

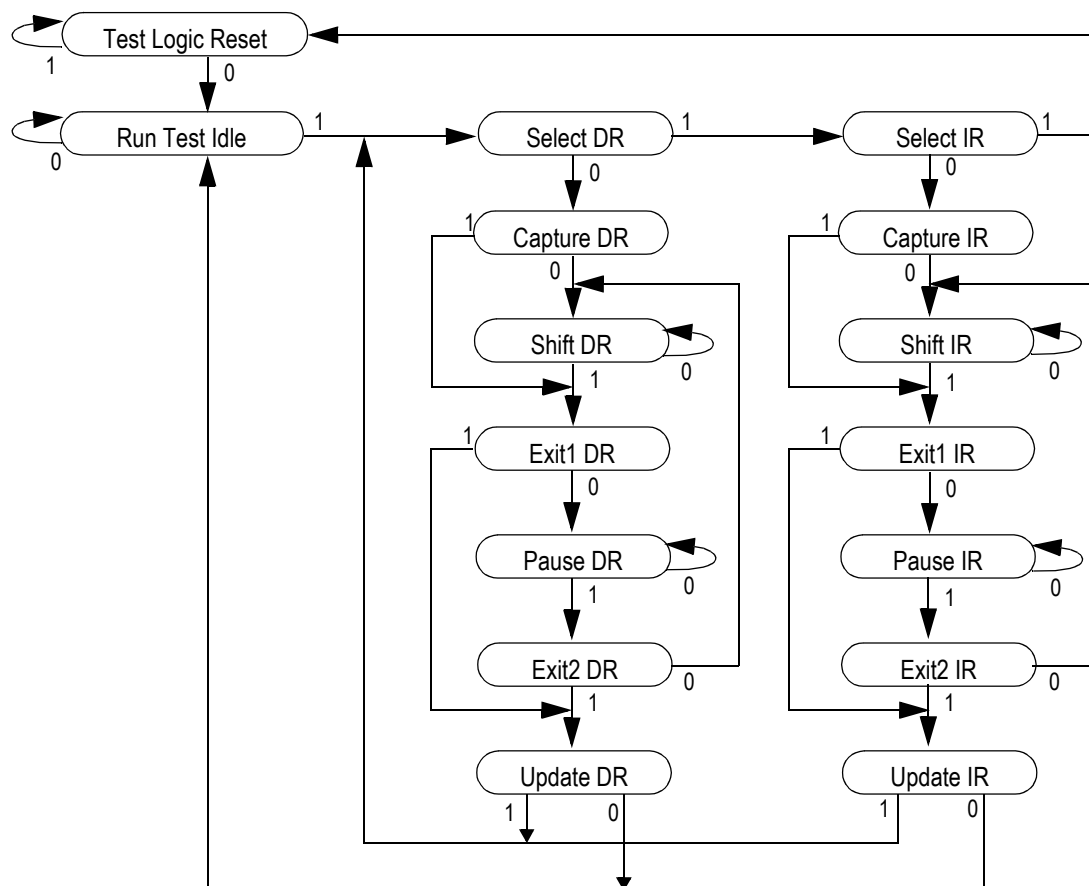
## Tap Controller Instruction Set

## Overview

There are two classes of instructions defined in the Standard 1149.1-1990; standard (Public) instructions, and device specific (Private) instructions. Some Public instructions are mandatory for 1149.1 compliance. Optional Public instructions must be implemented in prescribed ways. The TAP on this device may be used to monitor all input and I/O pads. This device will not perform INTEST but can perform the preload portion of the SAMPLE/PRELOAD command.

When the TAP controller is placed in Capture-IR state, the two least significant bits of the instruction register are loaded with 01. When the controller is moved to the Shift-IR state, the Instruction Register is placed between TDI and TDO. In this state the desired instruction is serially loaded through the TDI input (while the previous contents are shifted out at TDO). For all instructions, the TAP executes newly loaded instructions only when the controller is moved to Update-IR state. The TAP instruction set for this device is listed in the following table.

## JTAG Tap Controller State Diagram



## Instruction Descriptions

### BYPASS

When the BYPASS instruction is loaded in the Instruction Register, the Bypass Register is placed between TDI and TDO. This occurs when the TAP controller is moved to the Shift-DR state. This allows the board level scan path to be shortened to facilitate testing of other devices in the scan path.

### SAMPLE/PRELOAD

SAMPLE/PRELOAD is a Standard 1149.1 mandatory public instruction. When the SAMPLE / PRELOAD instruction is loaded in the Instruction Register, moving the TAP controller into the Capture-DR state loads the data in the RAMs input and I/O buffers into the Boundary Scan Register. Some Boundary Scan Register locations are not associated with an input or I/O pin, and are loaded with the default state identified in the BSDL file. Because the RAM clock is independent from the TAP Clock (TCK) it is possible for the TAP to attempt to capture the I/O ring contents while the input buffers are in transition (i.e. in a metastable state). Although allowing the TAP to sample metastable inputs will not harm the device, repeatable results cannot be expected. RAM input signals must be stabilized for long enough to meet the TAP's input data capture set-up plus hold time (t<sub>TS</sub> plus t<sub>TH</sub>). The RAM's clock inputs need not be paused for any other TAP operation except capturing



the I/O ring contents into the Boundary Scan Register. Moving the controller to Shift-DR state then places the Boundary Scan Register between the TDI and TDO pins. The Update-DR controller state transfers the contents of boundary scan cells into the holding register of each cell associated with an output pin on the RAM.

#### **EXTEST**

EXTEST is an IEEE 1149.1 mandatory public instruction. It is to be executed whenever the instruction register is loaded with all logic 0s. The EXTEST command does not block or override the RAM's input pins; therefore, the RAM's internal state is still determined by its input pins.

Typically, the Boundary Scan Register is loaded with the desired pattern of data with the SAMPLE/PRELOAD command. Then the EXTEST command is used to output the Boundary Scan Register's contents, in parallel, on the RAM's data output drivers on the falling edge of TCK when the controller is in the Update-IR state.

Alternately, the Boundary Scan Register may be loaded in parallel using the EXTEST command. When the EXTEST instruction is selected, the state of all the RAM's input and I/O pins, as well as the default values at Scan Register locations not associated with a pin, are sampled and transferred in parallel into the Boundary Scan Register on the rising edge of TCK in the Capture-DR state. Boundary Scan Register contents may then be shifted serially through the register using the Shift-DR command or the controller can be skipped to the Update-DR command. When the controller is placed in the Update-DR state, a RAM that has a fully compliant EXTEST function drives out the value of the Boundary Scan Register location associated with which each output pin.

#### **IDCODE**

The IDCODE instruction causes the ID ROM to be loaded into the ID register when the controller is in Capture-DR mode and places the ID register between the TDI and TDO pins in Shift-DR mode. The IDCODE instruction is the default instruction loaded in at power up and any time the controller is placed in the Test-Logic-Reset state.

#### **SAMPLE-Z/PRELOAD**

The SAMPLE-Z instruction operates exactly like SAMPLE/PRELOAD except that loading the SAMPLE-Z instruction forces all the RAM's output drivers, except TDO, to an inactive drive state (high-Z).

#### **RFU**

These instructions are reserved for future use. In this device they replicate the BYPASS instruction.

## JTAG TAP Instruction Set Summary

Instruction	Code	Description	Notes
EXTEST	000	Places the Boundary Scan Register between TDI and TDO.	1
IDCODE	001	Preloads ID Register and places it between TDI and TDO.	1, 2
SAMPLE-Z/ PRELOAD	010	Captures I/O ring contents. Places the Boundary Scan Register between TDI and TDO. Forces all Data and Clock output drivers to High-Z.	1
RFU	011	Do not use this instruction; Reserved for Future Use. Replicates BYPASS instruction. Places Bypass Register between TDI and TDO.	1
SAMPLE/ PRELOAD	100	Captures I/O ring contents. Places the Boundary Scan Register between TDI and TDO.	1
GSI Private	101	GSI Private instruction.	1
RFU	110	Do not use this instruction; Reserved for Future Use.	1
BYPASS	111	Places Bypass Register between TDI and TDO.	1

### Notes:

1. Instruction codes expressed in binary, MSB on left, LSB on right.
2. Default instruction automatically loaded at power-up and in Test-Logic-Reset state.

## JTAG Port Recommended Operating Conditions and DC Characteristics

Parameter	Symbol	Min.	Max.	Unit	Notes
Test Port Input High Voltage	$V_{IHT}$	$0.65 \cdot V_{DD}$	$V_{DD}+0.3$	V	1
Test Port Input Low Voltage	$V_{ILT}$	-0.3	$0.35 \cdot V_{DD}$	V	1
TMS, TCK and TDI Input Leakage Current	$I_{INTH}$	-100	2	uA	2
TMS, TCK and TDI Input Leakage Current	$I_{INTL}$	-2	2	uA	3
TDO Output Leakage Current	$I_{OLT}$	-2	2	uA	4
Test Port Output High Voltage	$V_{OHT}$	$V_{DDQ} - 100 \text{ mV}$	—	V	5, 6
Test Port Output Low Voltage	$V_{OLT}$	—	100 mV	V	7

### Notes:

1. Input Under/overshoot voltage must be  $-1 \text{ V} < V_i < V_{DD} + 1 \text{ V}$  with a pulse width not to exceed 20%  $t_{TKC}$ .
2.  $V_{DD} \geq V_{IN} \geq V_{IL}$
3.  $0 \text{ V} \leq V_{IN} \leq V_{IL}$
4. Output Disable,  $V_{OUT} = 0$  to  $V_{DD}$
5. The TDO output driver is served by the  $V_{DD}$  supply.
6.  $I_{OH} = -100 \text{ uA}$
7.  $I_{OL} = +100 \text{ uA}$

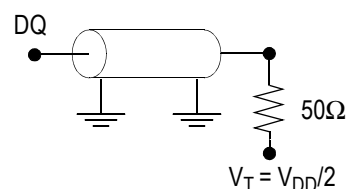
## JTAG Port AC Test Conditions

Parameter	Conditions
Input high level	$V_{DD} - 200 \text{ mV}$
Input low level	200 mV
Input slew rate	1 V/ns
Input reference level	$V_{DD}/2$
Output reference level	$V_{DD}/2$

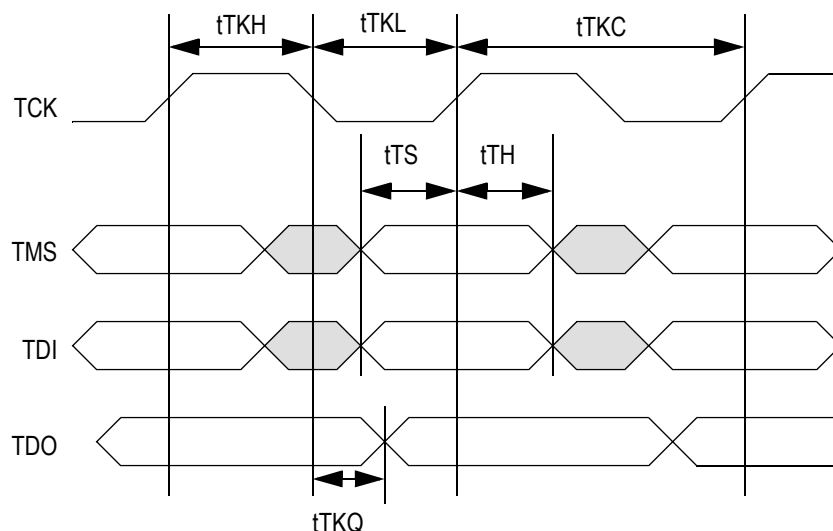
### Notes:

1. Include scope and jig capacitance.
2. Test conditions as as shown unless otherwise noted.

### JTAG Port AC Test Load



## JTAG Port Timing Diagram

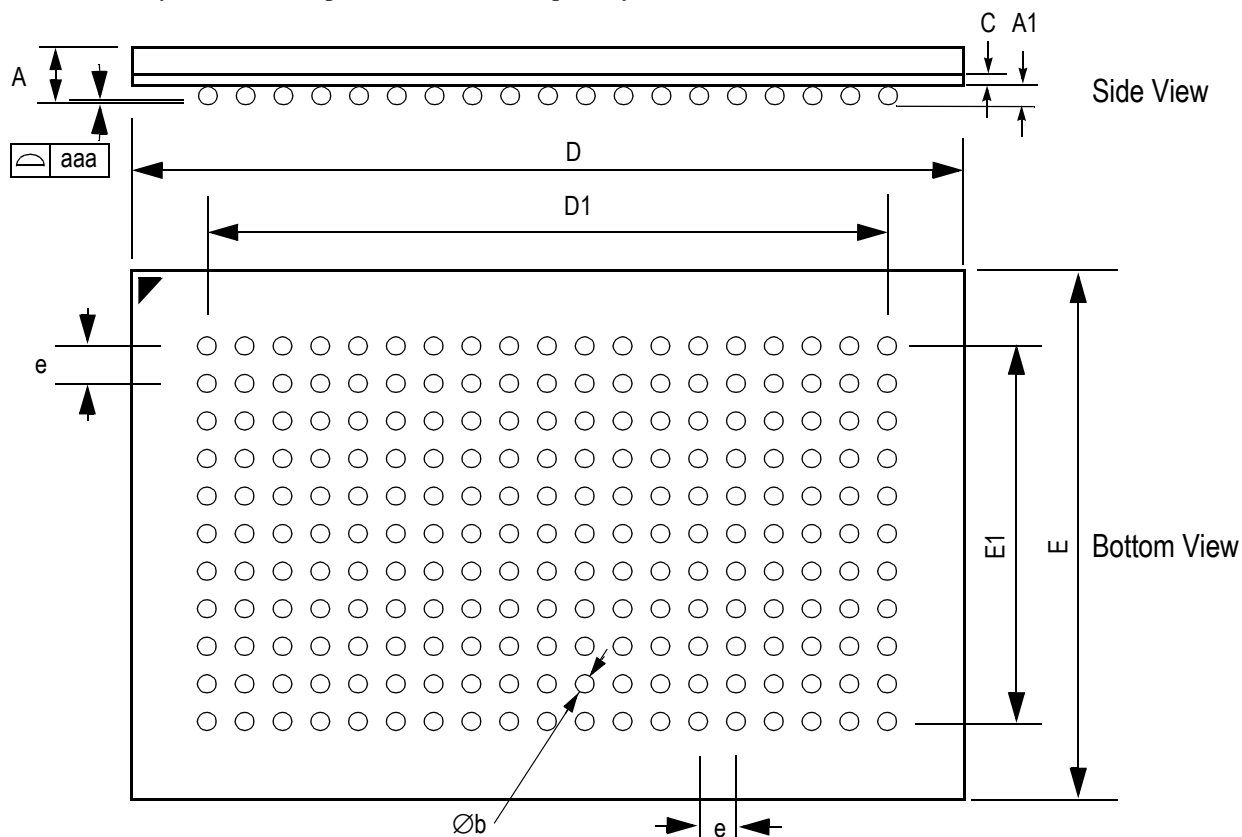


## JTAG Port AC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
TCK Cycle Time	$t_{TKC}$	50	—	ns
TCK Low to TDO Valid	$t_{TKQ}$	—	20	ns
TCK High Pulse Width	$t_{TKH}$	20	—	ns
TCK Low Pulse Width	$t_{TKL}$	20	—	ns
TDI & TMS Set Up Time	$t_{TS}$	10	—	ns
TDI & TMS Hold Time	$t_{TH}$	10	—	ns

## 209 BGA Package Drawing

14 mm x 22 mm Body, 1.0 mm Bump Pitch, 11 x 19 Bump Array



Symbol	Min	Typ	Max	Units
A			1.70	mm
A1	0.40	0.50	0.60	mm
Øb	0.50	0.60	0.70	mm
c	0.31	0.36	0.38	mm
D	21.9	22.0	22.1	mm
D1		18.0 (BSC)		mm
E	13.9	14.0	14.1	mm
E1		10.0 (BSC)		mm
e		1.00 (BSC)		mm
aaa		0.15		mm
Rev 1.0				

**Ordering Information—GSI SigmaRAM**

Org	Part Number <sup>1</sup>	Type	Package	Speed <sup>2</sup> (MHz/ ns)	T <sub>A</sub> <sup>3</sup>
256K x 72	GS8170S72B-333	Multi Mode $\Sigma 1 \times 1$ $\Sigma$ RAM	1 mm Pitch, 209-Pin BGA	333/5	C
256K x 72	GS8170S72B-300	Multi Mode $\Sigma 1 \times 1$ $\Sigma$ RAM	1 mm Pitch, 209-Pin BGA	300/5.5	C
256K x 72	GS8170S72B-250	Multi Mode $\Sigma 1 \times 1$ $\Sigma$ RAM	1 mm Pitch, 209-Pin BGA	250/6.7	C
256K x 72	GS8170S72B-333I	Multi Mode $\Sigma 1 \times 1$ $\Sigma$ RAM	1 mm Pitch, 209 Pin BGA	333/5	I
256K x 72	GS8170S72B-300I	Multi Mode $\Sigma 1 \times 1$ $\Sigma$ RAM	1 mm Pitch, 209-Pin BGA	300/5.5	I
256K x 72	GS8170S72B-250I	Multi Mode $\Sigma 1 \times 1$ $\Sigma$ RAM	1 mm Pitch, 209-Pin BGA	250/6.7	I
512K x 36	GS8170S36B-333	Multi Mode $\Sigma 1 \times 1$ $\Sigma$ RAM	1 mm Pitch, 209-Pin BGA	333/5	C
512K x 36	GS8170S36B-300	Multi Mode $\Sigma 1 \times 1$ $\Sigma$ RAM	1 mm Pitch, 209-Pin BGA	300/5.5	C
512K x 36	GS8170S36B-250	Multi Mode $\Sigma 1 \times 1$ $\Sigma$ RAM	1 mm Pitch, 209-Pin BGA	250/6.7	C
512K x 36	GS8170S36B-333I	Multi Mode $\Sigma 1 \times 1$ $\Sigma$ RAM	1 mm Pitch, 209-Pin BGA	333/5	I
512K x 36	GS8170S36B-300I	Multi Mode $\Sigma 1 \times 1$ $\Sigma$ RAM	1 mm Pitch, 209-Pin BGA	300/5.5	I
512K x 36	GS8170S36B-250I	Multi Mode $\Sigma 1 \times 1$ $\Sigma$ RAM	1 mm Pitch, 209-Pin BGA	250/6.7	I
1Mx 18	GS8170S18B-333	Multi Mode $\Sigma 1 \times 1$ $\Sigma$ RAM	1 mm Pitch, 209-Pin BGA	333/5	C
1Mx 18	GS8170S18B-300	Multi Mode $\Sigma 1 \times 1$ $\Sigma$ RAM	1 mm Pitch, 209-Pin BGA	300/5.5	C
1Mx 18	GS8170S18B-250	Multi Mode $\Sigma 1 \times 1$ $\Sigma$ RAM	1 mm Pitch, 209-Pin BGA	250/6.7	C
1Mx 18	GS8170S18B-333I	Multi Mode $\Sigma 1 \times 1$ $\Sigma$ RAM	1 mm Pitch, 209-Pin BGA	333/5	I
1Mx 18	GS8170S18B-300I	Multi Mode $\Sigma 1 \times 1$ $\Sigma$ RAM	1 mm Pitch, 209-Pin BGA	300/5.5	I
1Mx 18	GS8170S18B-250I	Multi Mode $\Sigma 1 \times 1$ $\Sigma$ RAM	1 mm Pitch, 209-Pin BGA	250/6.7	I

**Notes:**

- Customers requiring delivery in Tape and Reel should add the character “T” to the end of the part number. Example: GS817x72B-300T.
- The speed column indicates the cycle frequency (MHz) of the device in Pipelined mode and the latency (ns) in Flow Through mode. Each device is Pipeline/Flow Through mode selectable by the user.
- T<sub>A</sub> = C = Commercial Temperature Range. T<sub>A</sub> = I = Industrial Temperature Range.